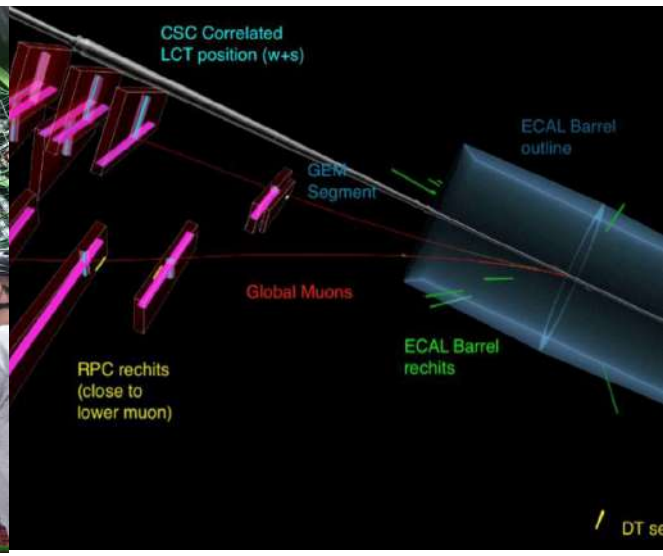
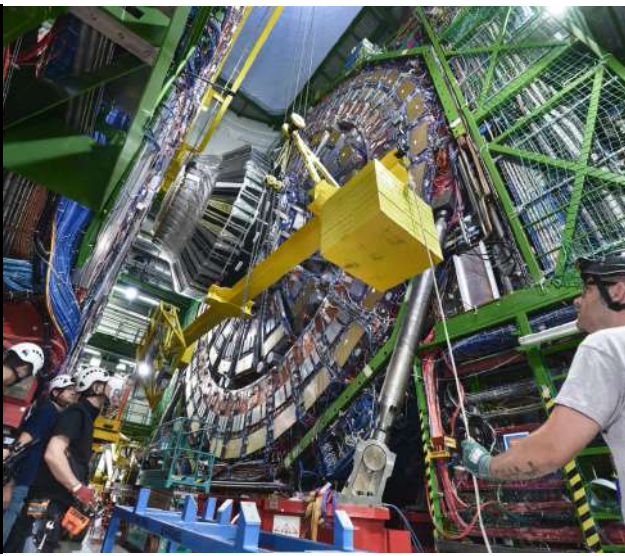
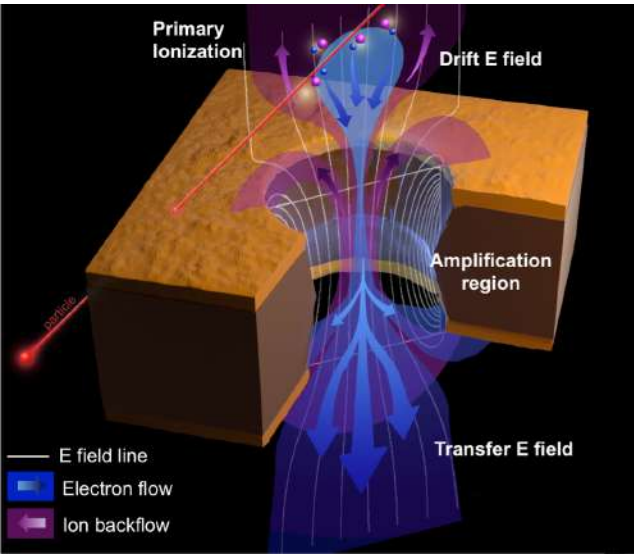
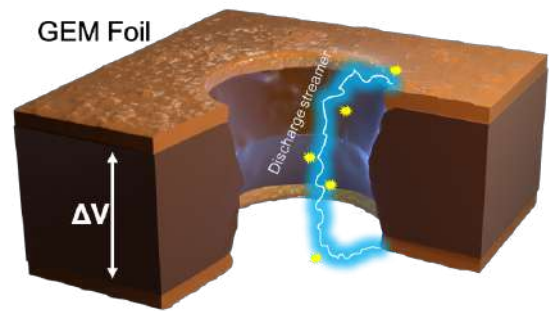


Study and Mitigation of Discharges in CMS Triple-GEM Detectors

Jeremie MERLIN on behalf of the CMS Muon group

3rd International Conference on Detector Stability and Aging Phenomena in Gaseous Detectors

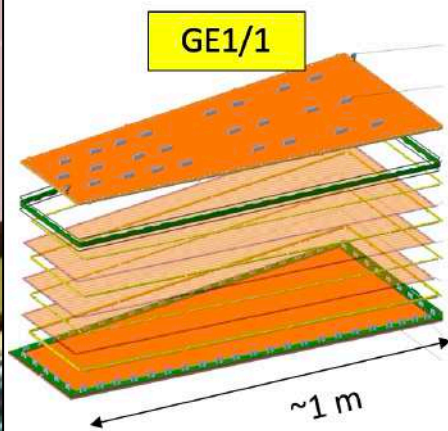
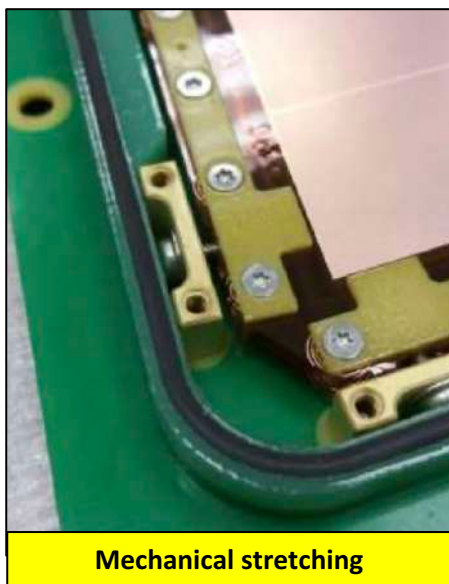
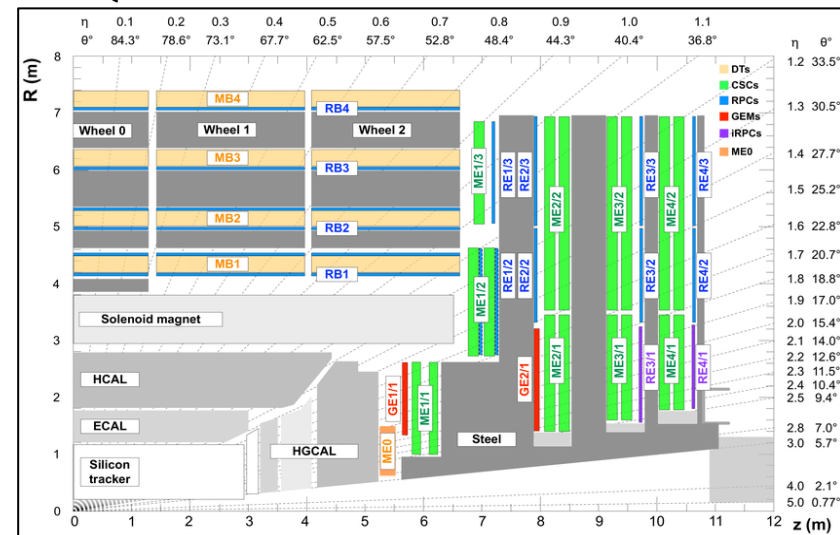
November 2023



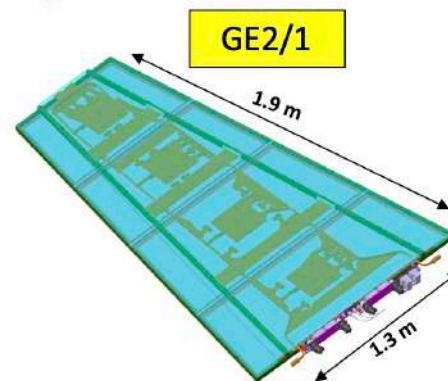
GEM upgrade projects for CMS:

- 3 detector projects in the forward muon endcap
 - All based on same triple-GEM technology and same material
 - GEM configuration 3(drift)/1/2/1 mm
 - Baseline gas: Ar/CO₂ (70/30%)
 - Max. background rates from a few kHz/cm² (GE2/1) to 150 kHz/cm² (ME0)
- About 600 m² of GEM foils for about 1.5 M of RO channels

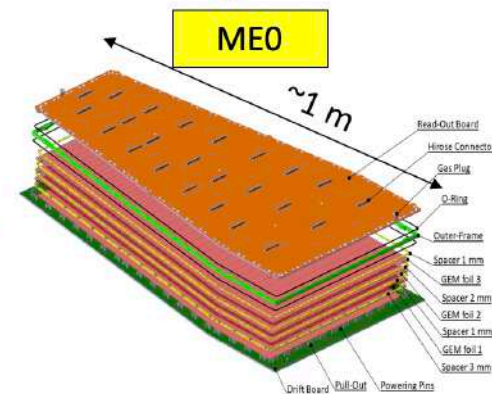
CMS Quadrant



GE1/1:
144 detectors



GE2/1:
288 detectors



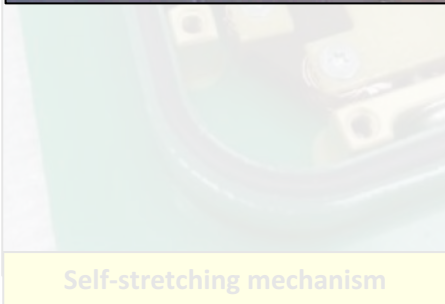
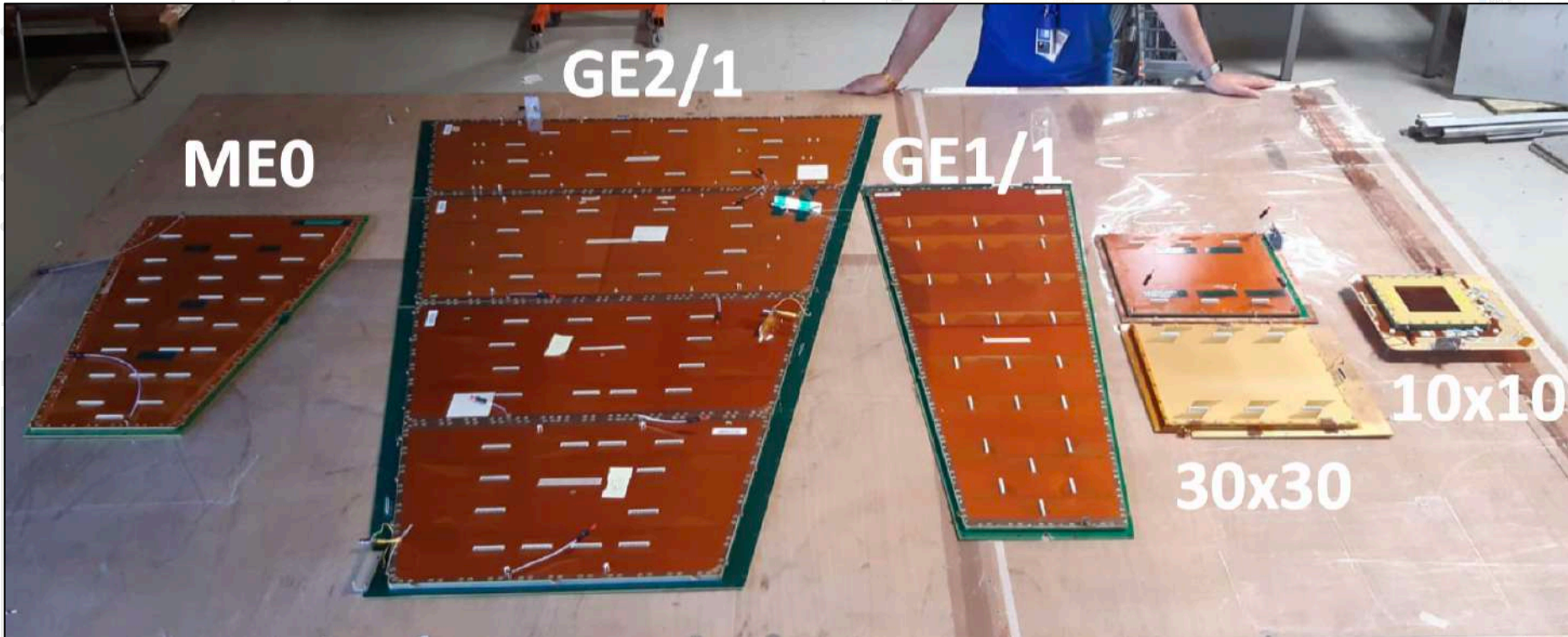
ME0:
216 detectors

Introduction

GEM upgrade projects for CMS:

- 3 detector projects in the forward muon endcap

η	0.1	0.2	0.3	0.4	0.5	0.6	0.7	0.8	0.9	1.0	1.1
θ	84.3°	78.6°	73.1°	67.7°	62.5°	57.5°	52.8°	48.4°	44.3°	40.4°	36.8°
R (m)	[Graph showing detector radii vs pseudorapidity]										



GE1/1:
144 detectors



GE2/1:
288 detectors



MEO:
216 detectors

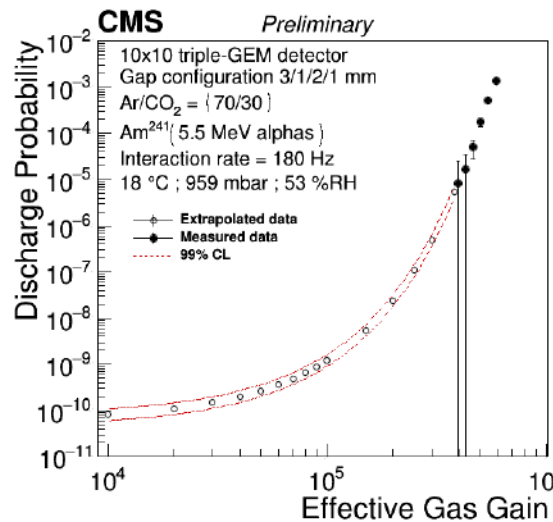
Measuring the probability of discharges:

- Tests in laboratory (alpha particles) with both small and large detectors
- Tests in neutron facilities with CMS-like particle background

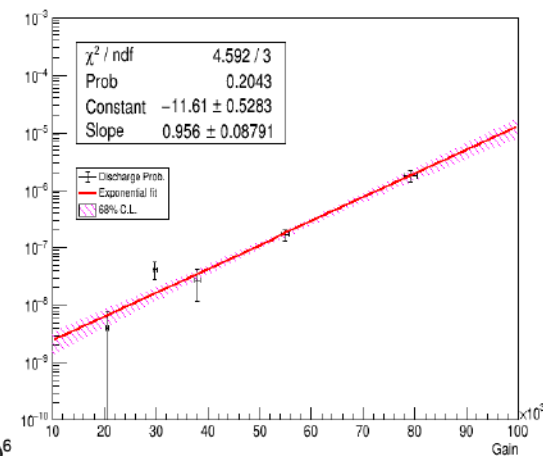
Discharge probability at $G=3.5 \times 10^4$ (HIP)

- 10x10@GDD Lab: 1.5×10^{-10}
- GE1/1(KR)@904 GEM Lab: 1.7×10^{-8}
- 10x10@CHARM: 2.85×10^{-9}

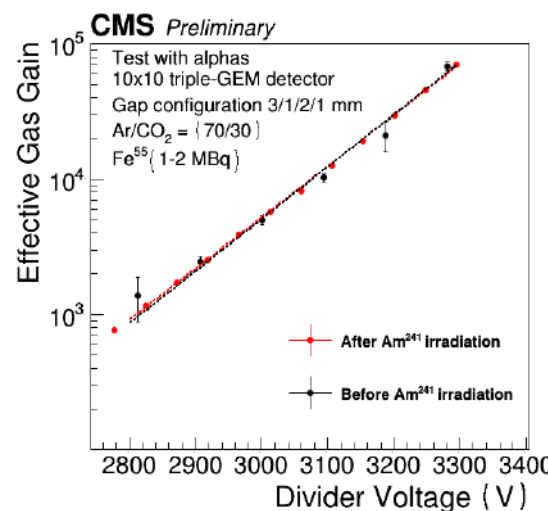
- No temporary or permanent degradation of the detector performance could be measured after alpha irradiation, nor in neutron environment (up to 500 discharges/cm²)



J. Merlin, CMS-TDR-016, 2017

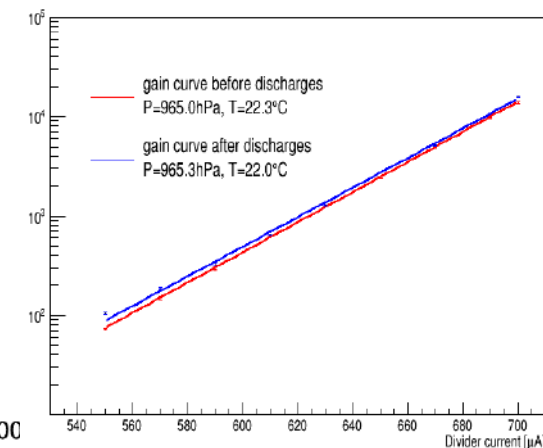


I. Yoon, LHC KCMS Workshop, 09/01/2019



J. Merlin, CMS-TDR-016, 2017

Gain curves before/after discharge Prob. measurement

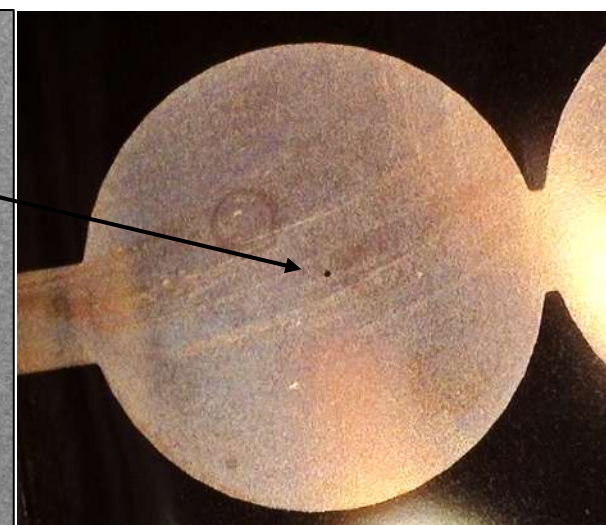
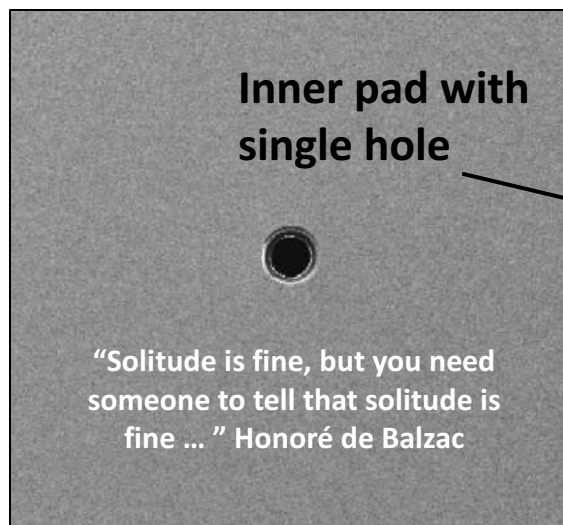
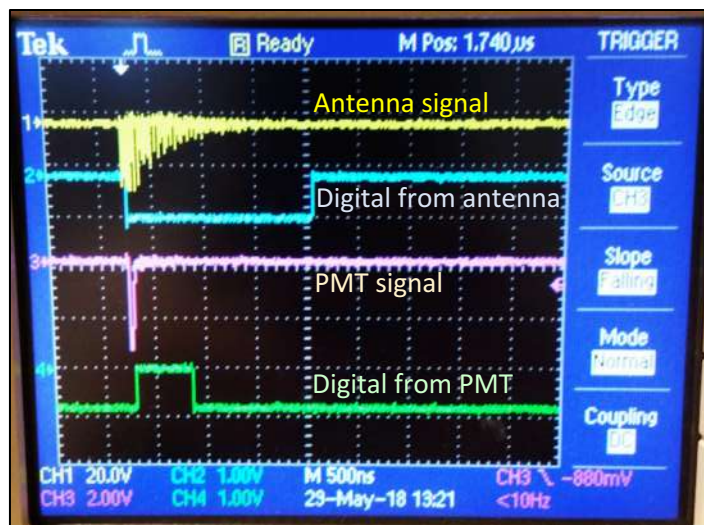
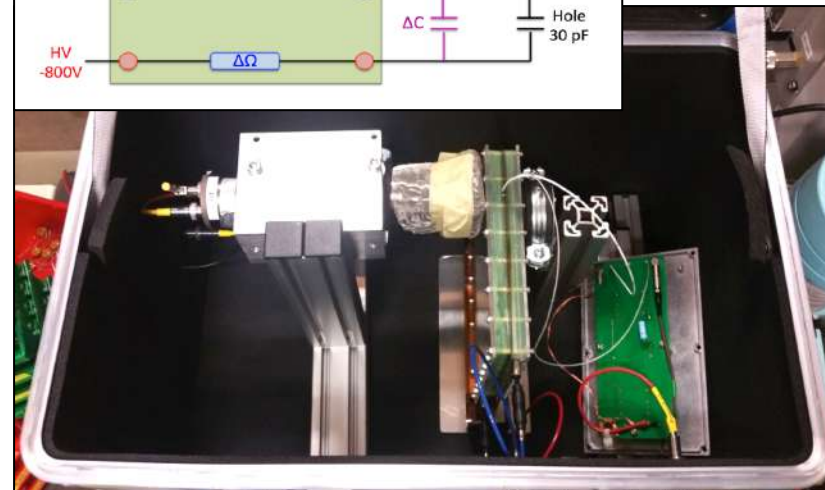
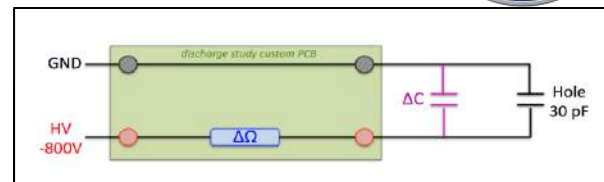


I. Yoon, LHC KCMS Workshop, 09/01/2019

Discharge Effects

Specific study on single GEM hole systems:

- Special GEM foil design with single hole to control the conditions of discharges and isolate the elements that play a role
 - 30 pF base capacitance
 - Possibility to operate up to 800 V (stable)
- Discharges triggered with a Cd109 source
- Discharge identification made by cross-comparing PMT signals (light) and antenna signals (EM)

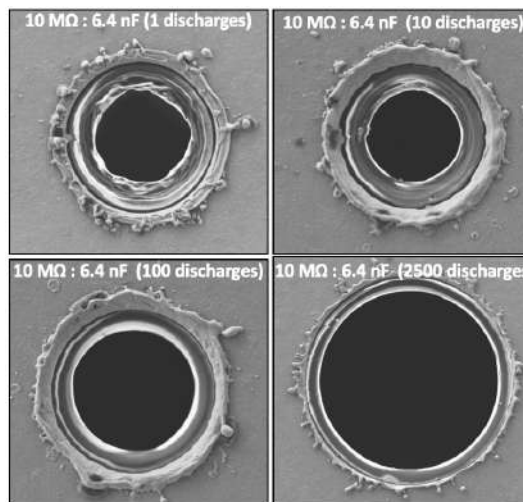
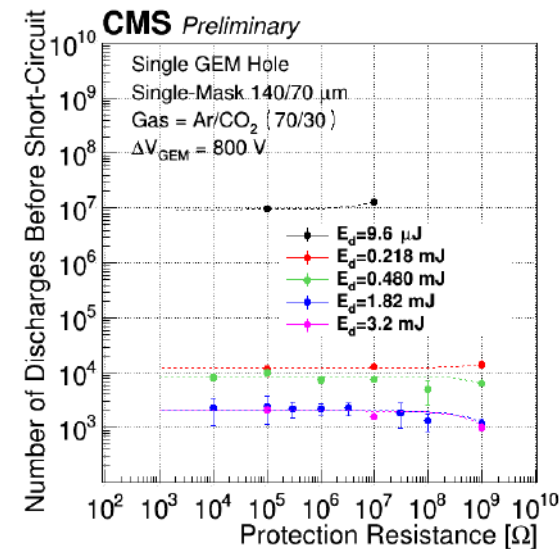
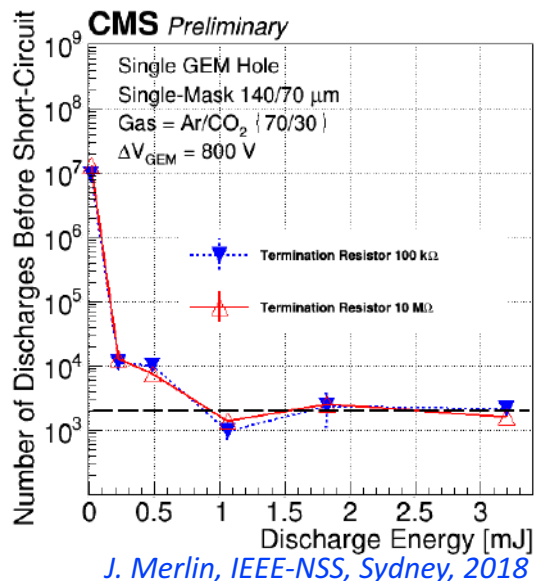
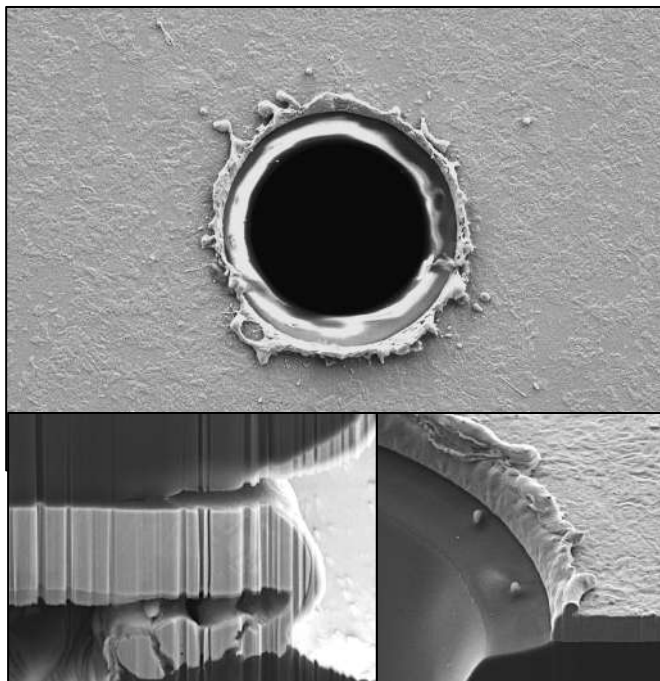


“Solitude is fine, but you need someone to tell that solitude is fine ...” Honoré de Balzac

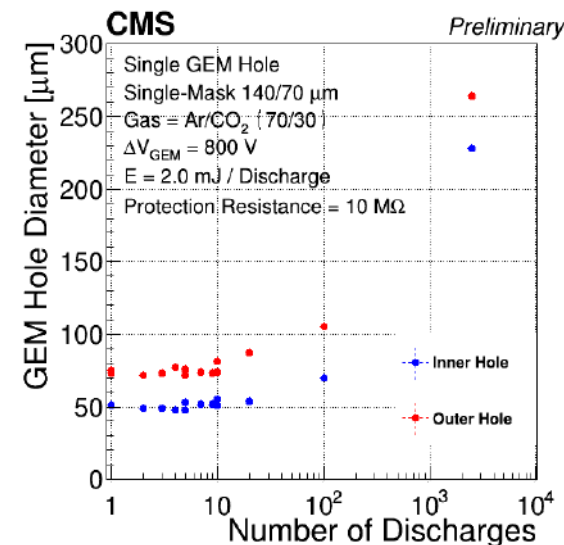
Discharge Effects

• **Test results:**

- Measurements reveal high resistance to discharges, even at high energy ($>10^3$)
- Increase of the hole diameter after 10-20 accumulated discharges



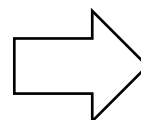
J. Merlin, IEEE-NSS, Sydney, 2018



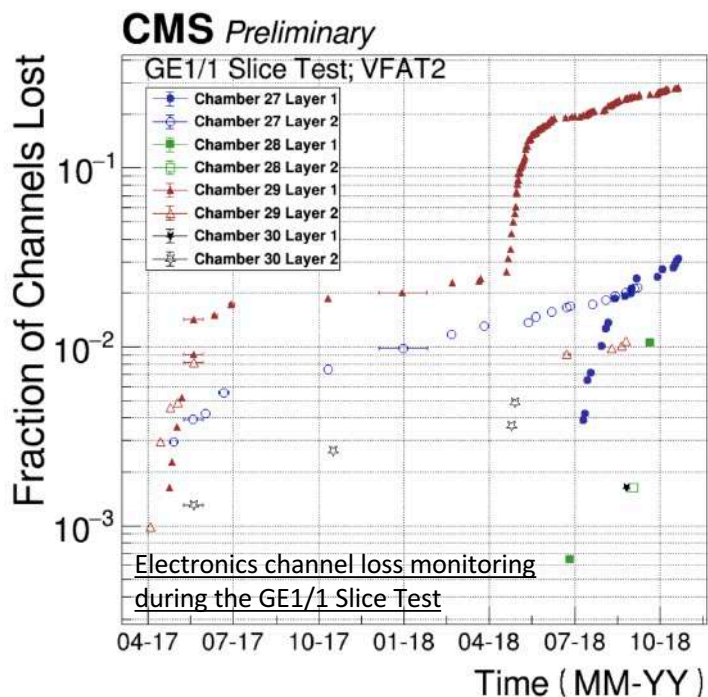
J. Merlin, IEEE-NSS, Sydney, 2018

GE1/1 Slice test (2017-2018)

- First operational experience in the real CMS environment
- First observation of discharge propagation
- Experienced VFAT3 channel loss

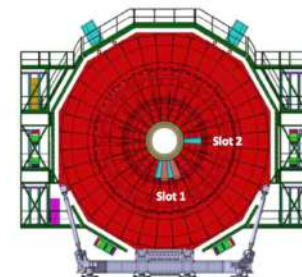


Start of a new discharge R&D campaign to cope with discharge propagation
 (+ define new setups and protocols to reproduce the problem in the lab)



Channel loss :

- GEM discharges are normally confined within the GEM holes
- Discharges can propagate toward the readout board
- Possible damage of the electronics



$$\text{Channel loss} \propto \text{Discharge probability} \times \text{Propagation probability} \times \text{Damage probability}$$

The most effective mitigation consists of reducing the probability of **discharge propagation**

Discharge Propagation

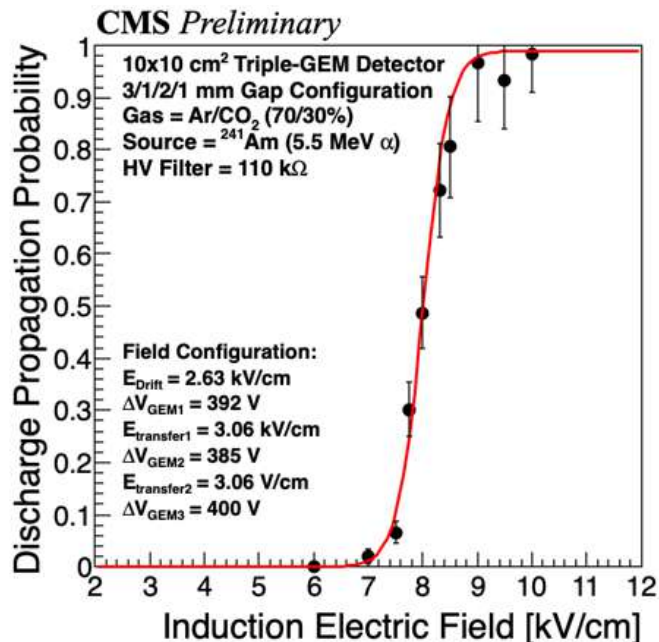
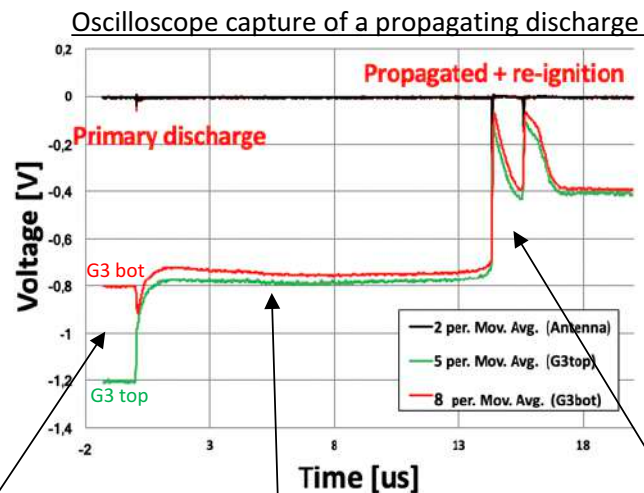
Propagation process:

Step1: the **primary discharge** develops inside the GEM holes (temporary short circuit)

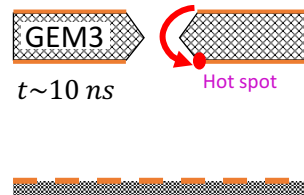
Step2: a **precursor current** arises from the hot spot created by the primary discharge (thermionic emission enhanced by the Schottky effect)

Step 3: the precursor current grows from the energy available in the foil to become a streamer

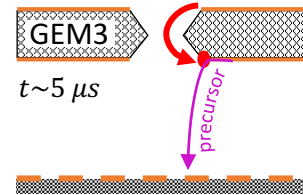
→ **secondary discharge** between the GEM and the RO



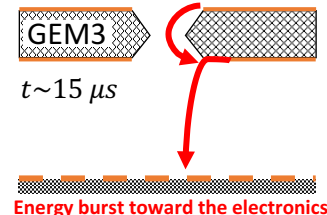
Step 1: initial GEM discharge



Step 2: precursor current



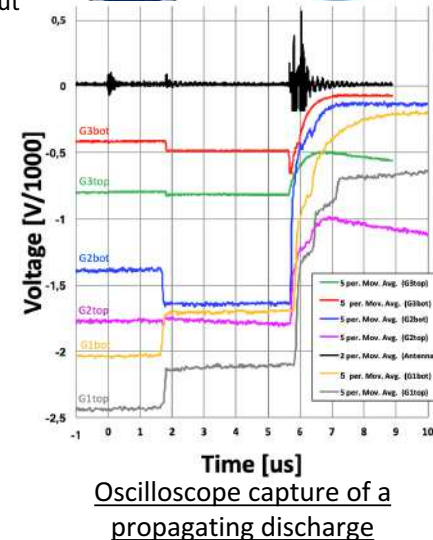
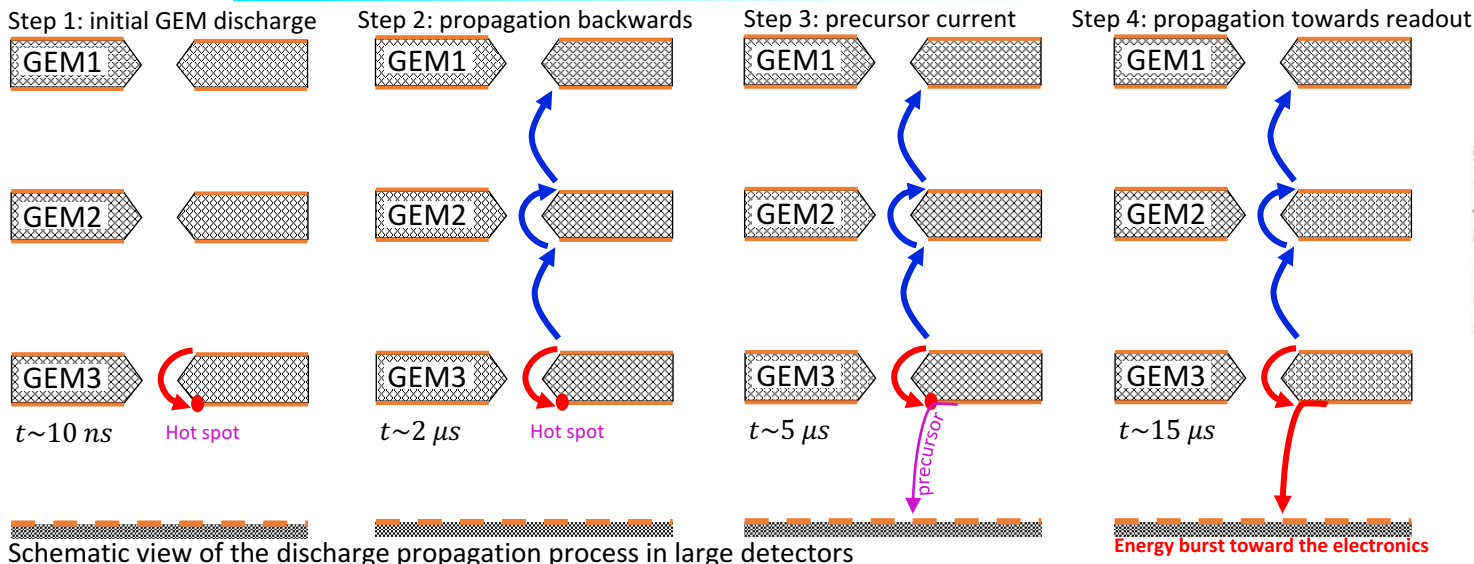
Step 3: discharge propagation



Schematic view of the discharge propagation process

The probability to observe a discharge propagation in small detectors is **insignificant** below inductions fields of **7 kV/cm**:
 → CMS GEM typical induction field = **4.1 - 4.5 kV/cm**

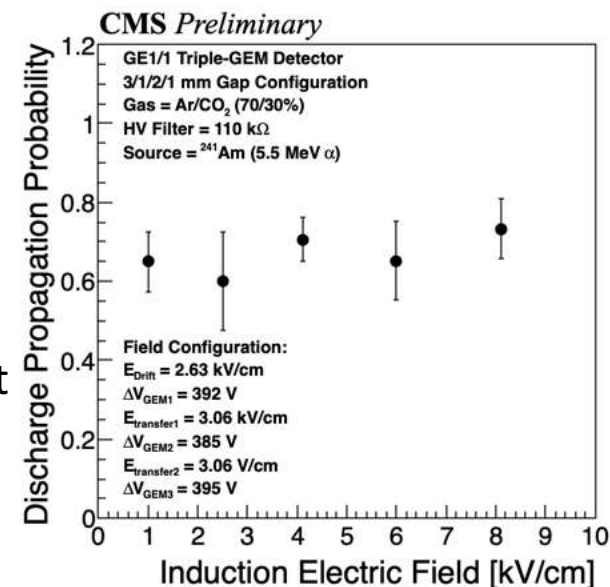
Discharge Propagation



More complex propagation in large detectors:

- The primary discharge is systematically followed with a propagation backward **GEM2** and **GEM1**
- The backward propagation “gives” the primary discharge the strength to propagate **toward the readout** even at **low induction fields**
- After a full propagation, the electronics is connected (via short circuits in the gas) to all the GEM electrodes

The probability to observe a discharge propagation in large detectors is **significant** even at **low inductions fields**



Discharge Propagation

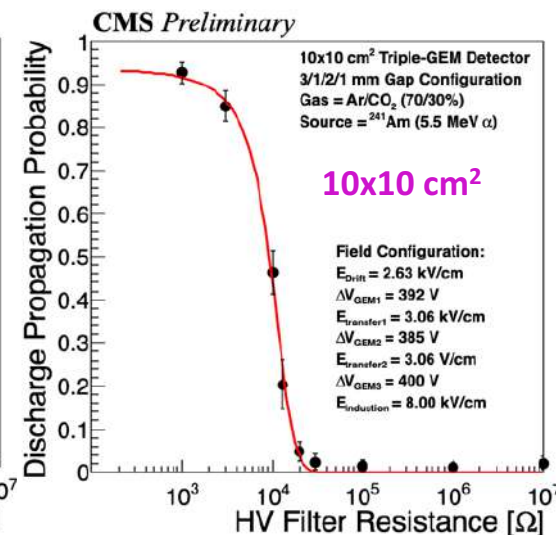
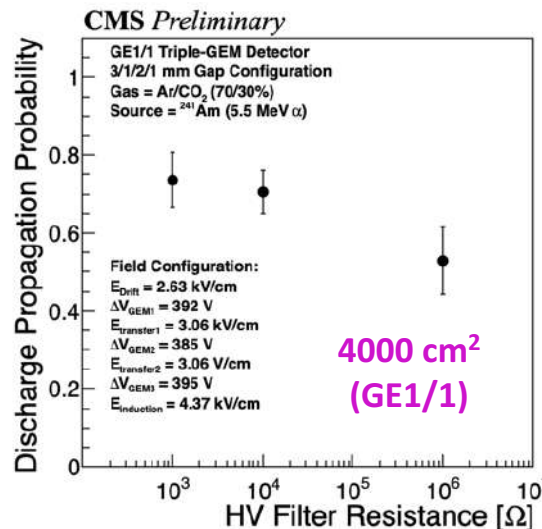
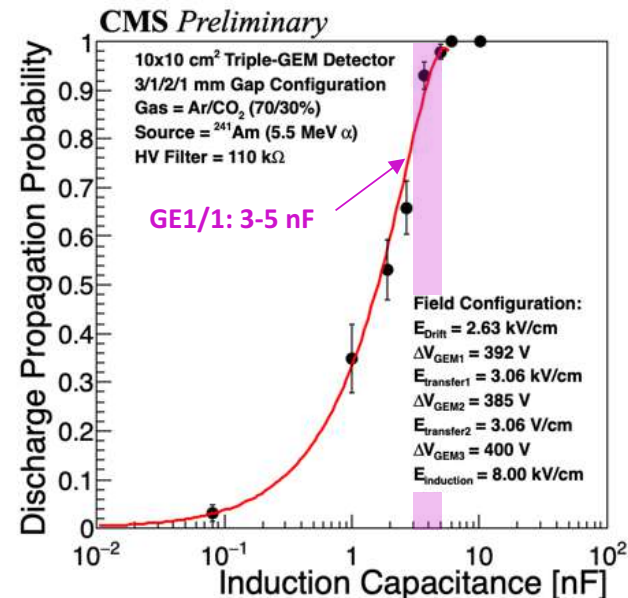
Large reservoir of energy:

- The probability for a discharge to propagate depends on the **gap capacitance**
- A large gap capacitance means more energy to **feed the precursor current** and trigger the streamer development
- GE1/1 foils typically have enough **energy stored** in the gap to trigger the propagation, even at low induction field

Influence from outside:

- The energy stored “outside” the GEM foil can participate to the discharge propagation
- The **filter resistance** helps to prevent energy transfer to the foil

GE1/1-size foils contain enough energy to maintain an almost-systematic discharge propagation without the help of external energy



Discharge Mitigations

$$\text{Channel loss} \propto \text{Discharge probability} \times \text{Propagation probability} \times \text{Damage probability}$$

Discharge Probability



Intrinsic to gaseous technologies
 Low probability with triple-GEM ($\sim 10^{-9}$)

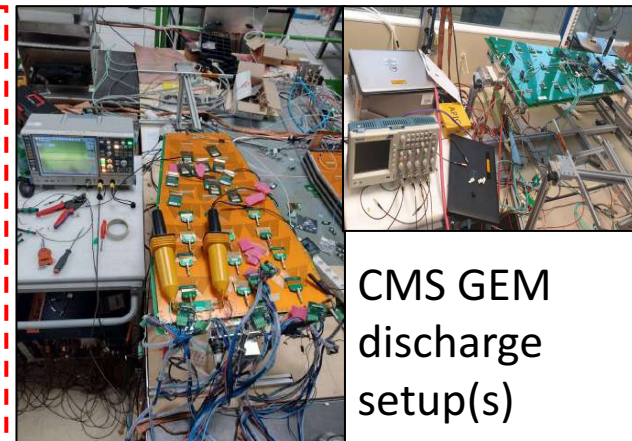
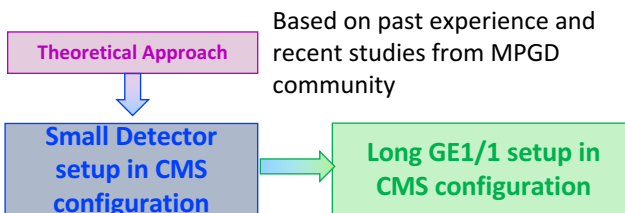
It is a “no pain no gain” parameter

Propagation Probability



Complex process depending on:

- De-coupling circuits
- Gap Capacitance
- Electric Fields



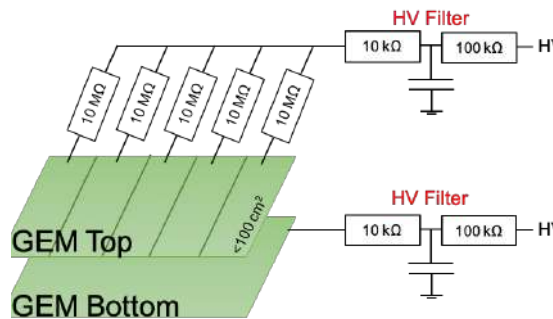
CMS GEM discharge setup(s)

- Full size prototypes
 - Modified PCBs to allow for alpha irradiation
 - Antenna + HF-HV probes for discharge monitoring
 - Increased HV on GEM3 to trigger discharges at interesting rate (few Hz)
- Became a standard setup for discharge investigations

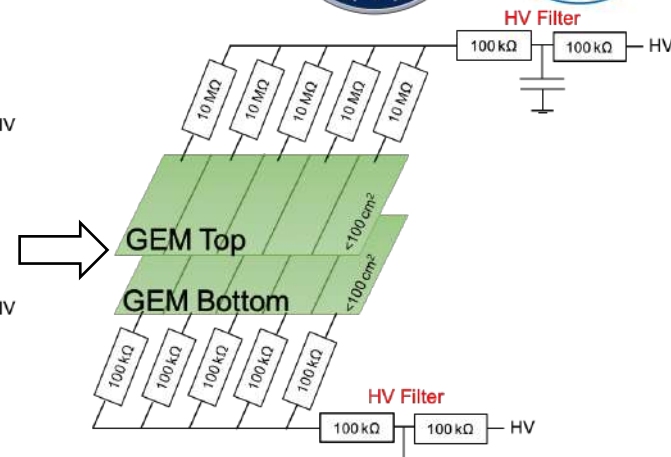
GEM Double-Segmentation:

Basic principle:

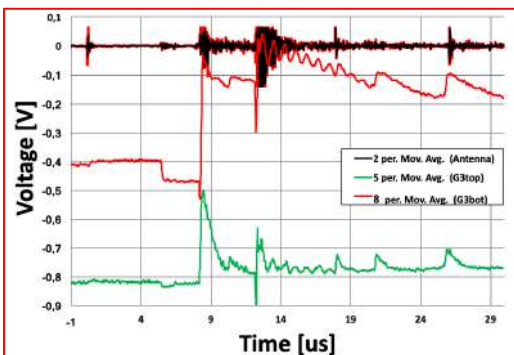
- **Top segmentation** : GEM protection against regular discharges
- **Bottom segmentation**: protection against discharge propagation



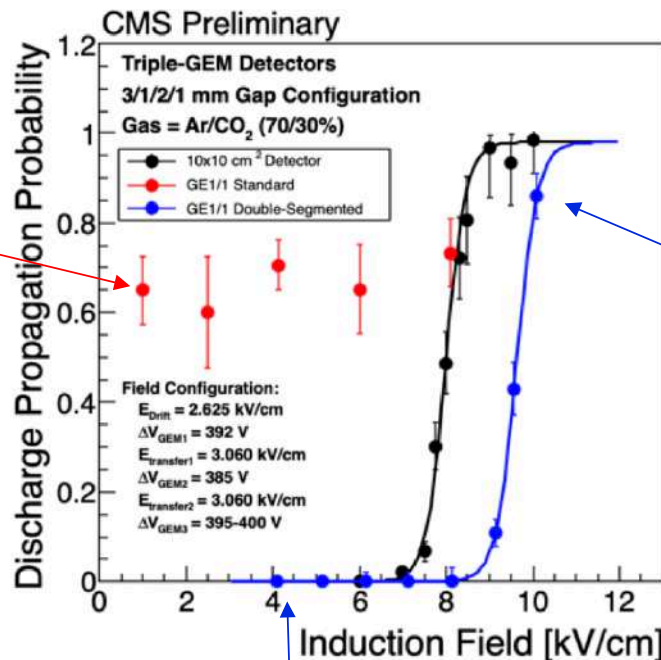
“Single-segmented” GEM foil concept



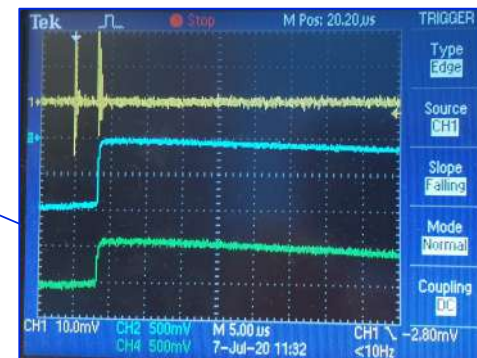
“Double-segmented” GEM foil concept



Single-segmented large setup:
 → Complex multi-stage propagation process even at low HV



Upper limit at 4.12 kV/cm: $P_{d,propa} < 3 \times 10^{-4}$



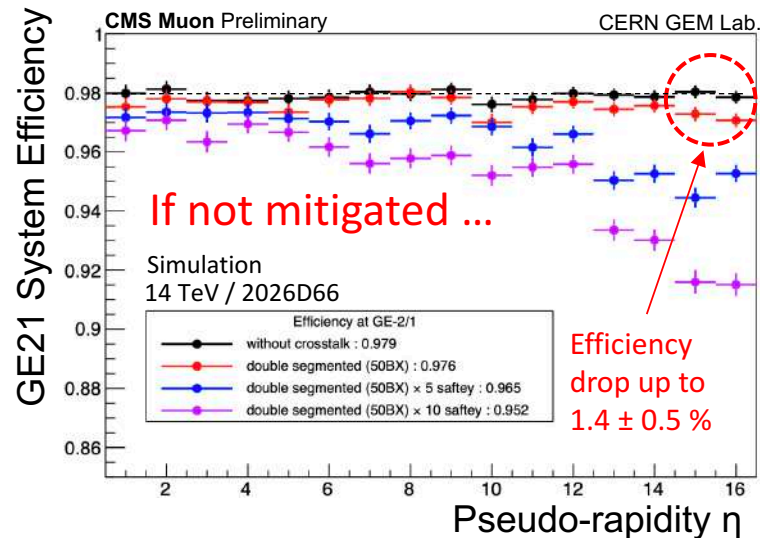
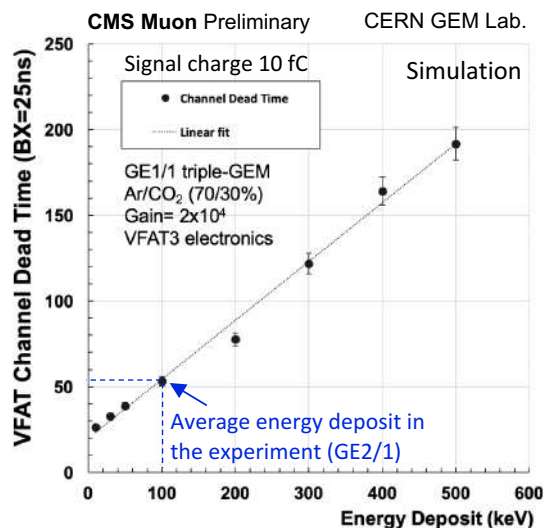
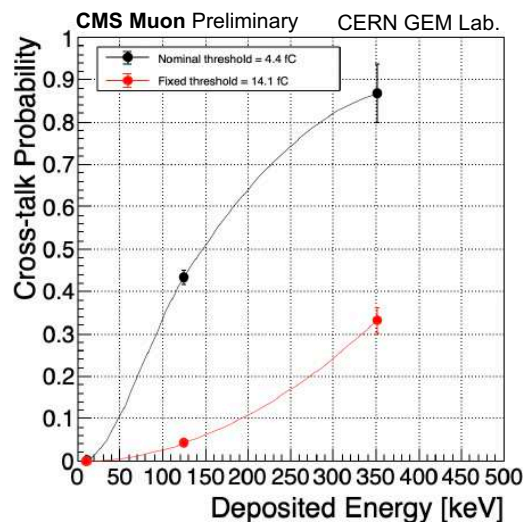
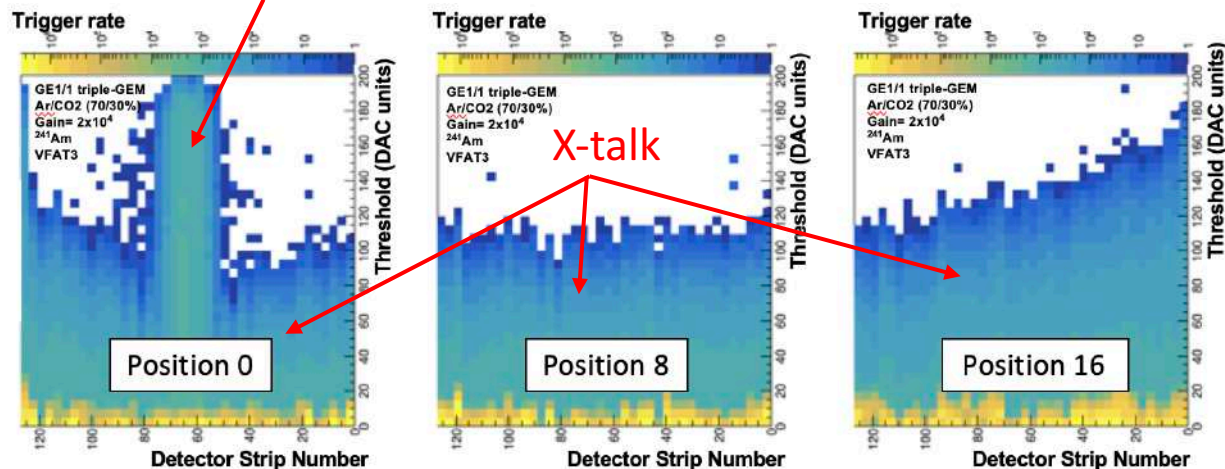
Double-segmented large setup:
 → Simple propagation process only at high HV
 → Similar profile as 10x10 propagations

Discharge Mitigations

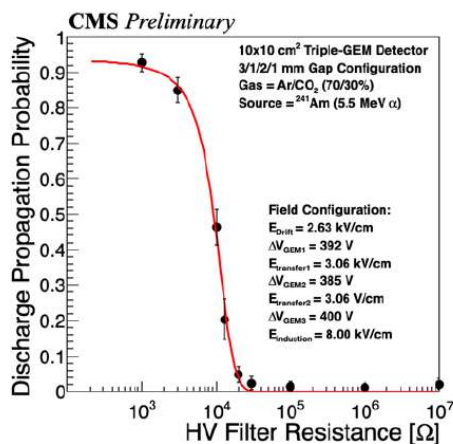
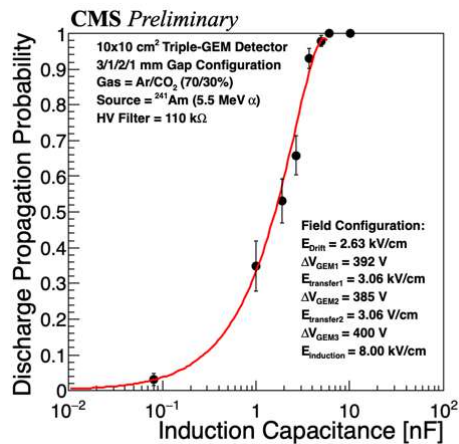
Side effect:

- The use of double-segmented foil in front of the RO board creates a strong cross-talk effect with HIPs
- The resulting parasitic signals induce a deadtime in the electronics
- With no mitigations, cross-talk could affect the detector efficiency by a few % at highest eta regions

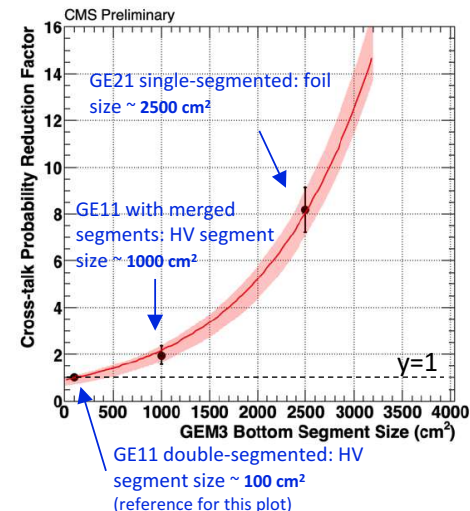
HIP Source signal



Discharge Mitigations



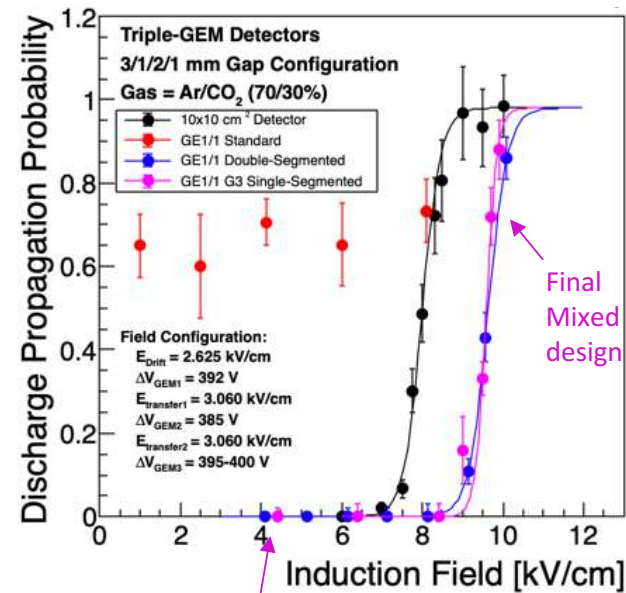
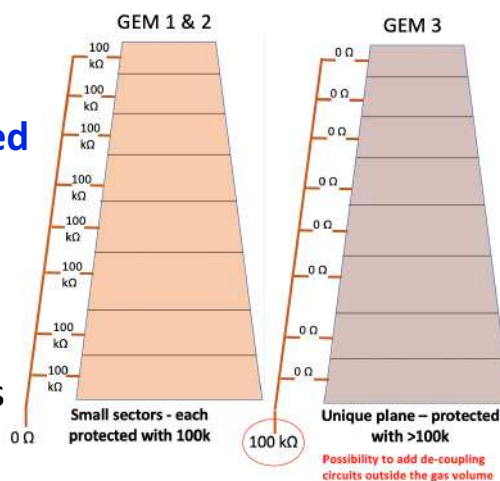
Side effect
X-talk



Mitigate discharge Propag.

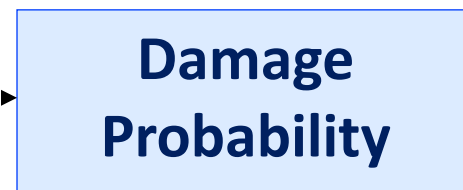
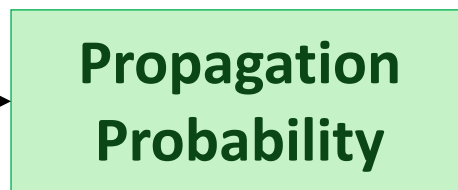
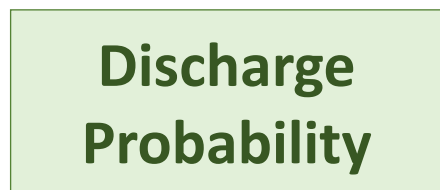
Mitigate X-talk

- Introducing the final configuration based on the **“mixed” design**:
- GEM1 and GEM2 are **double-segmented** to prevent the **discharge propagation**
- GEM3 is **single-segmented** to minimize the **crossstalk**
 - The foil is actually double-segmented but the bottom segments are merged together using **0 Ω jumpers**



Upper limit at 4.12 kV/cm: Pd_{propa} < 3x10⁻⁴

Discharge Mitigations

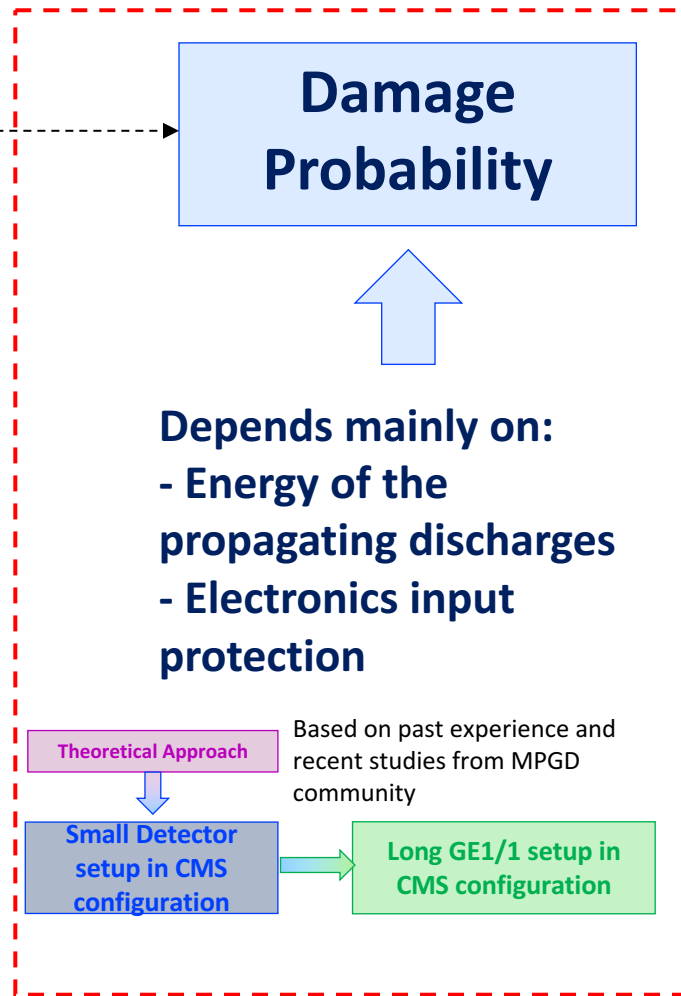


Intrinsic to gaseous technologies
 Low probability with triple-GEM ($\sim 10^{-9}$ - 10^{-10})
 It is a “no pain no gain” parameter

Understood the process of propagation in large detectors
 → Mainly driven by the large induction capacitance

Found 2 ways to mitigate discharge propagation:
 → Reduce foil capacitance (segmentation)
 → Increase filter resistance (resistive de-coupling)

Depends mainly on:
 - Energy of the propagating discharges
 - Electronics input protection



Discharge Mitigations

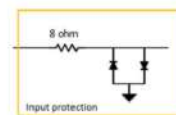
Front-End protection:

- VFAT3 + custom plugin cards (HV3b)
- 3 variants developed for GE1/1
 - Baseline V2 (no external protection)
 - V3 with External 300-400 Ω
 - V4 with external diodes to GND
- Further optimization implemented for GE2/1 and later ME0 (new hybrid design)
- All variants thoroughly tested in laboratory + test beams

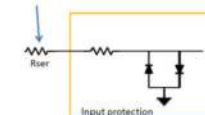
Early Conclusions (2019):

- working as expected in 10x10 detector with controlled discharge energy
- Different situation when operating with large detectors
 - Increased propagation energy
 - Parasitic effects from the other electronics components

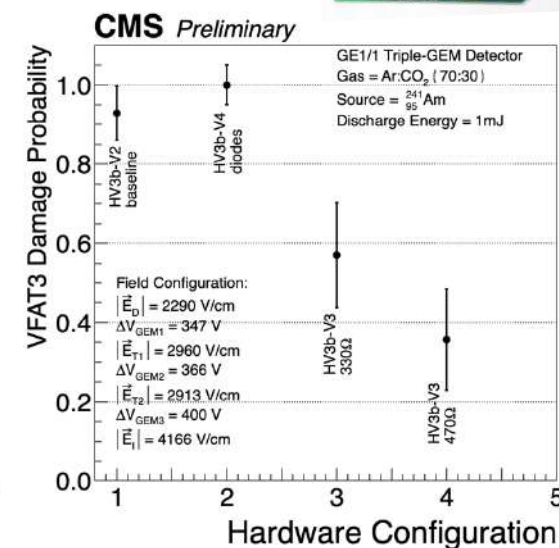
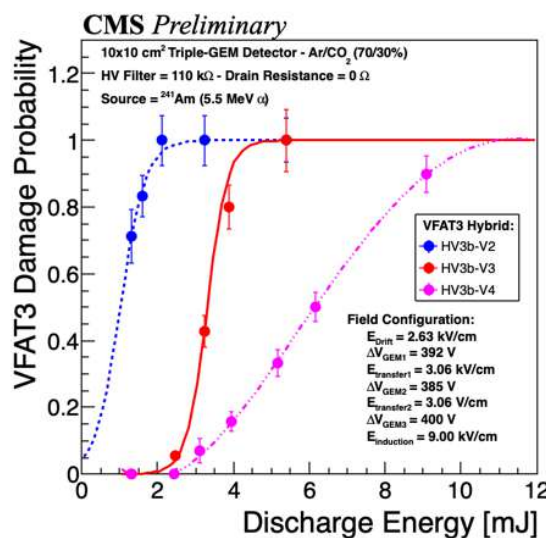
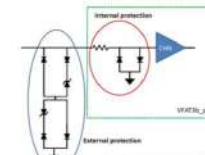
HV3b_V2
Initial baseline
 Internal input protection only (diode)
 Channels burnt with $E > 28 \mu\text{J}/\text{disc}$



HV3b_V3
 Ext. input protection ($R=330 \Omega$)
 OK after 500 ESD 470 $\mu\text{J}/\text{disc}$
 X-talk +15%; Noise +20%
 No radiation issues expected

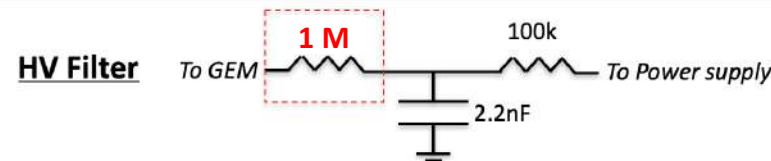
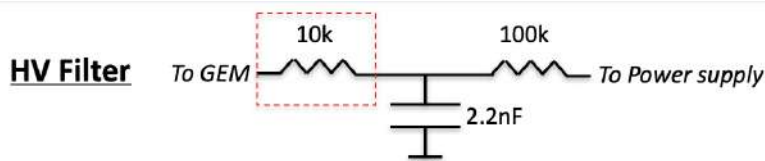
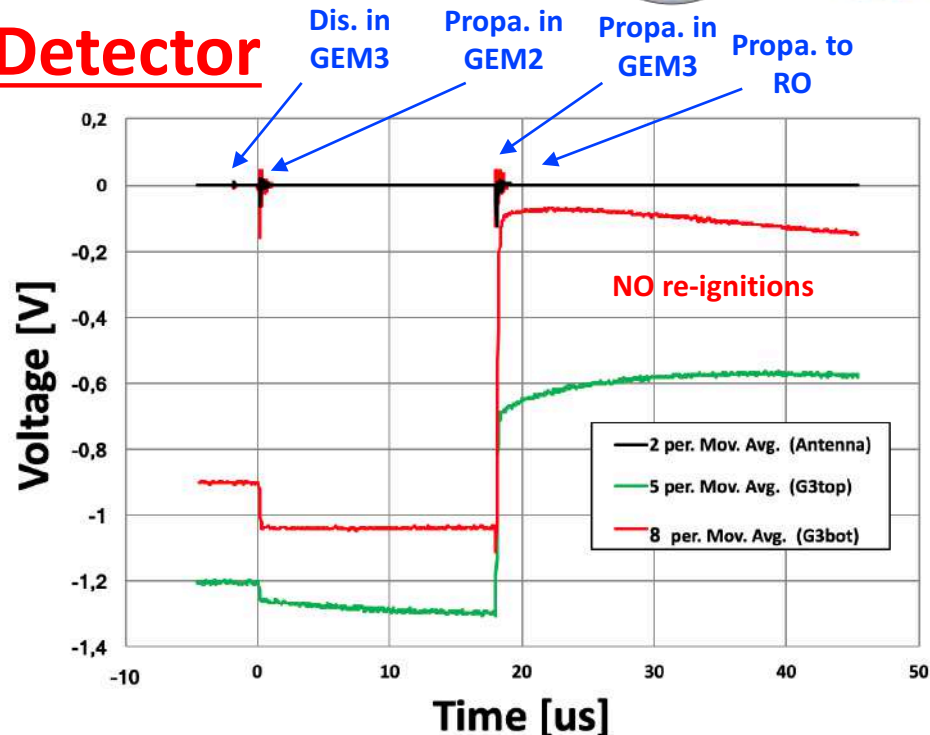
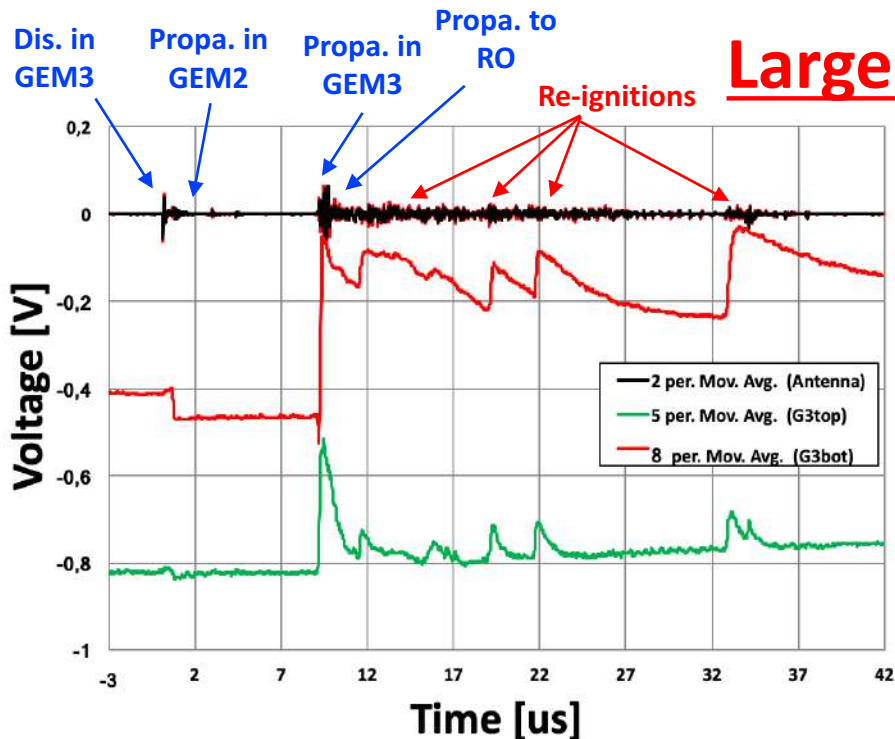


HV3b_V4
 Ext. input protection (diodes)
 OK after 540 ESD 470 $\mu\text{J}/\text{disc}$
 No increase of noise observed
 Rad Hard studies OK (10Mrad)



Discharge Mitigations

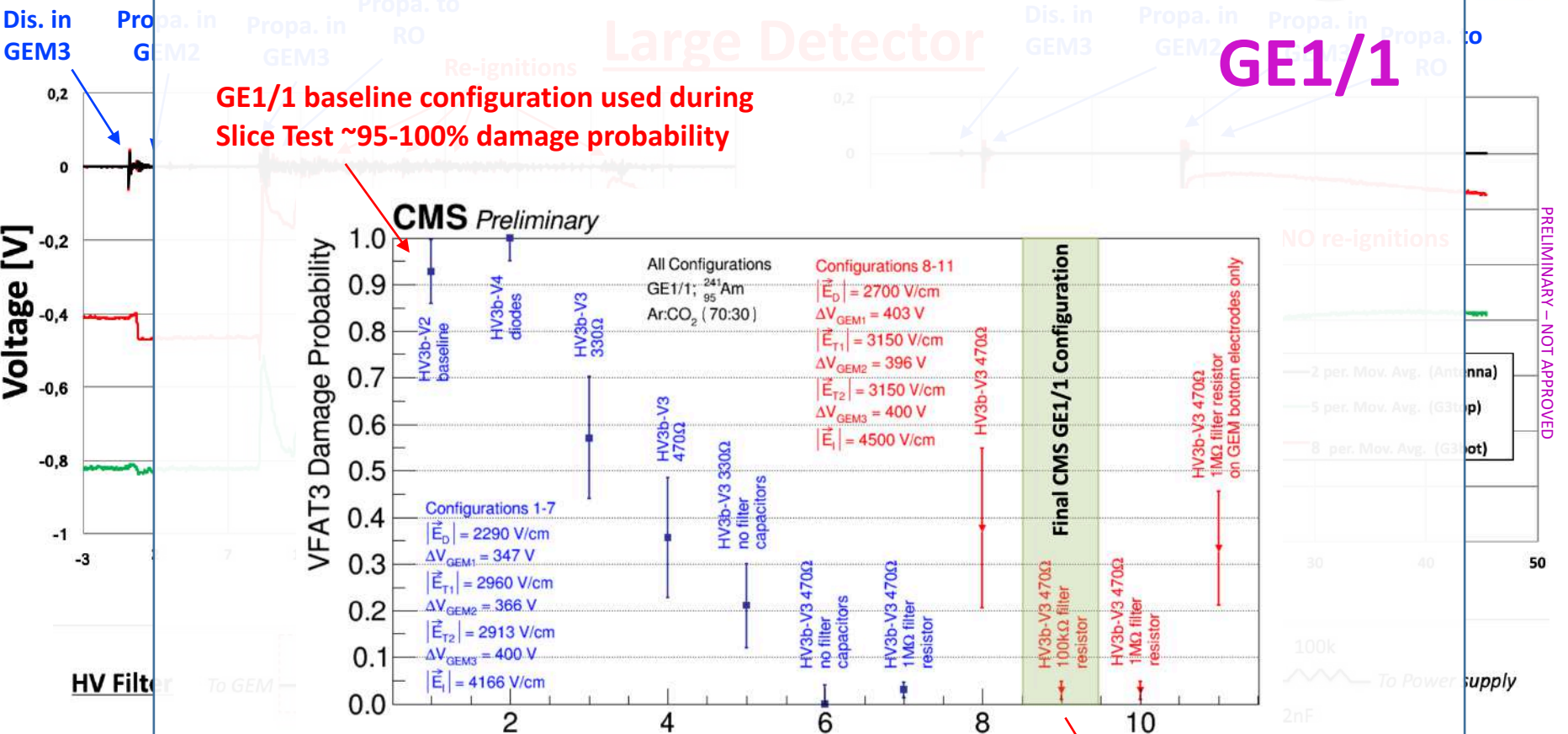
Large Detector



In-depth investigations with large detectors:

- Additional studies indicated that the damage probability in large detectors is mainly due to propagation re-ignitions
- Re-ignitions are fed by the energy stored in the filter capacitance → can be mitigated by tuning the filter resistance → can reduce by a factor 5 the damage probability

Discharge Mitigations

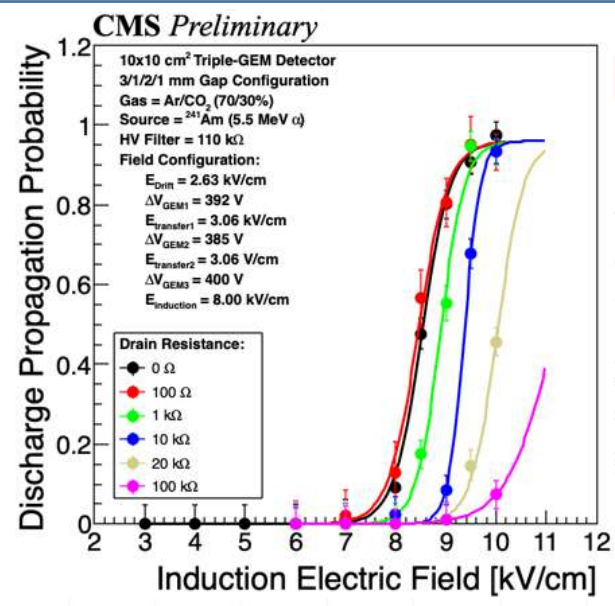
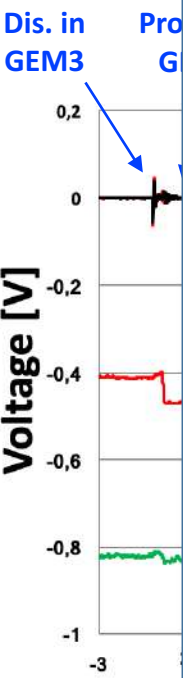


In-depth investigations with large detectors:

- Additional studies indicated that the damage probability in large detectors is mainly due to propagation re-ignitions
- Re-ignitions are fed by the energy stored in the capacitors. This can be mitigated by tuning the filter resistance → can reduce by a factor 10 the damage probability

Improved GE1/1 configuration = 3% damage probability
 → Improved VFAT input protection (R=470)
 → Suppressed re-ignition (HV resistor >100 k)

Discharge Mitigations

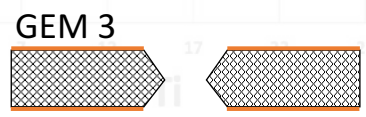


GE2/1 & ME0

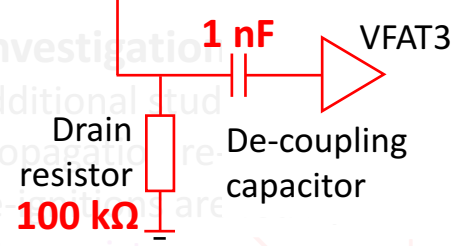
An additional layer of discharge protection on the readout side:

→ The discharge propagation can be stopped at the input of the RO strips using a drain resistor:

- the **precursor current** induced before the discharge propagation runs through the drain resistor
- the **voltage drop** across the drain resistor temporarily suppresses the **induction field**
- the precursor current is quenched and the discharge propagation is **stopped before reaching the RO strips**



In-depth



GE21 plugin card



→ with drain resistors as low as 100 kΩ, the propagation probability is reduced by a **factor > 10²**

PRELIMINARY - NOT APPROVED

Mitigations Issues

However: some problems appeared when implementing the mitigations on full size detectors

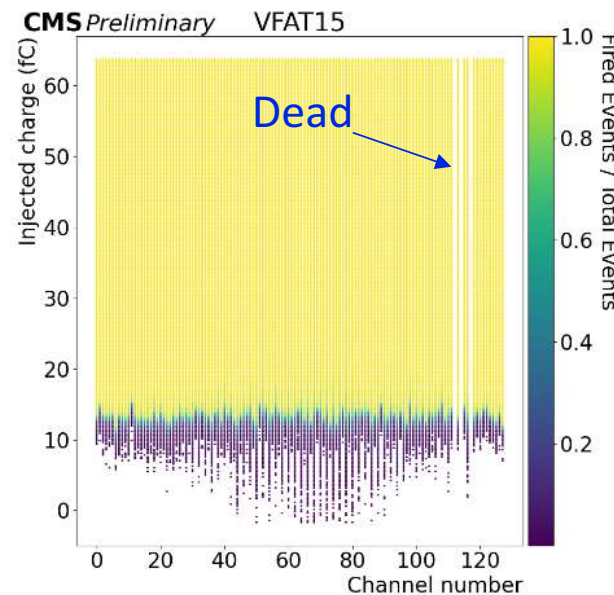
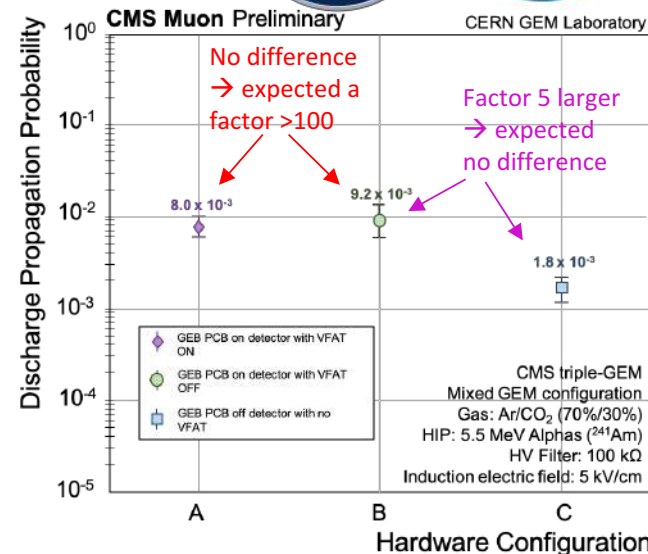
Problem 1: the addition of the **GEB** increases the propagation probability by a factor ~ 5
GEM Electronics Board

Problem 2: the use of the de-coupling circuit on the VFAT plug-in card does **not** reduce the propagation probability as expected

Problem 3: the final prototypes of GE2/1 plug-in cards still suffered dead channels, not only during operation but also during the production process when performing HV curing of GEM3 (a.k.a Megger test)

In summary:

- Increased propagation probability when connecting the final front-end electronics
- No reduction of the propagation probability when using the new plug-in card
- Increased susceptibility to discharges



PROBLEM 1

Without on-detector electronics

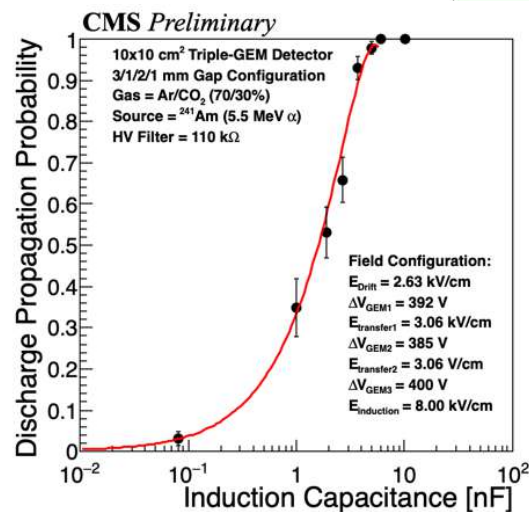
		area cm ²	Calculated		Voltage V	Energy mJ
			Capa nF	Measured Capa nF		
induction	GE1/1-L	4090	2.84	2.88	420	0.25
	10x10	115	0.08	0.08043859	420	0.01
foil	GE1/1	100	4.7	-	400	0.38
	10x10	115	5.47	5.6	400	0.44



Adding GEB electronics

With on-detector electronics

		area cm ²	Calculated	with electronics/cooling/chimney		Voltage V	Energy mJ
			Capa nF	Measured Capa nF	Energy mJ		
induction	GE1/1-L	4090	2.84	8.57	0.76	420	0.76
	10x10	115	0.08	3.2	0.28	420	0.28
foil	GE1/1	100	4.7	-	0.38	400	0.38
	10x10	115	5.47	5.6	0.44	400	0.44



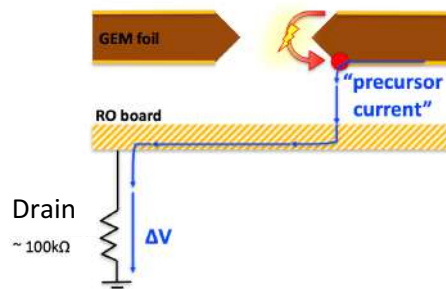
GEB capacitance effects

- Past measurement indicated that GEB (GEM Electronics Board) and electronics can add parasitic capacitance to the induction gap
 → With an increase of 5-6 nF the propagation probability can be multiplied by a large factor (based on 10x10 measurements)
- Not possible to mitigate without a significant re-design of the electronics and PCBs
 → But not a real problem if the detector is in the mixed-design configuration

PROBLEM 2 & 3

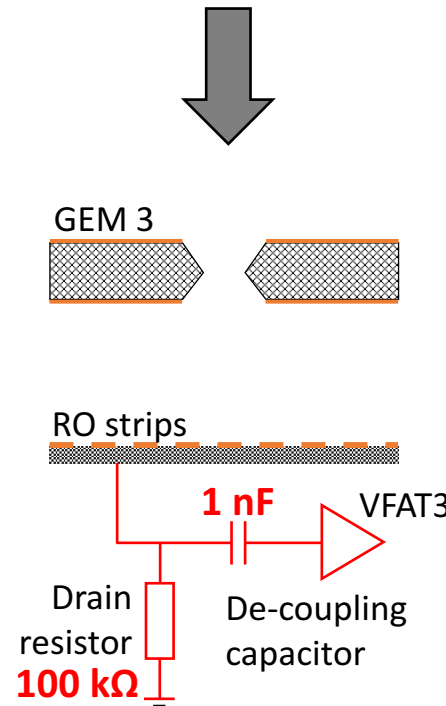
Drain resistor solution:

- Use of a drain resistor on the RO strips is a powerful mitigation solution
- Measured clear improvement with 10x10 detectors when connecting all RO strips to a single resistive output

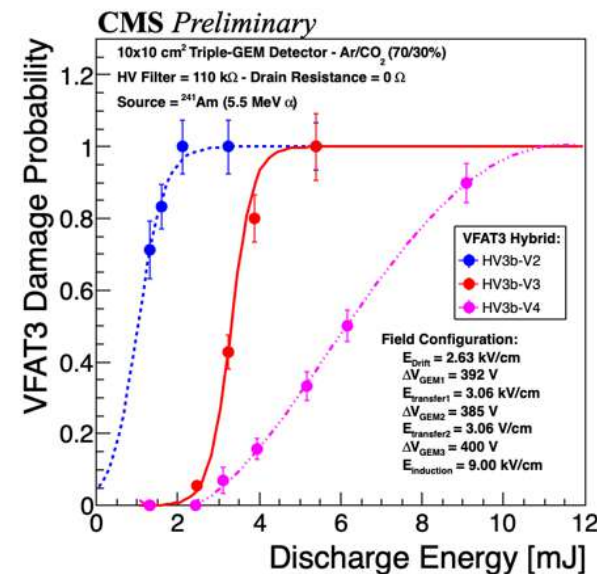
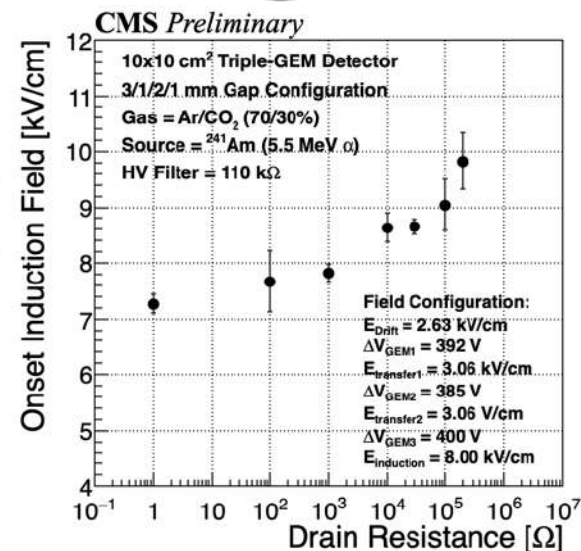


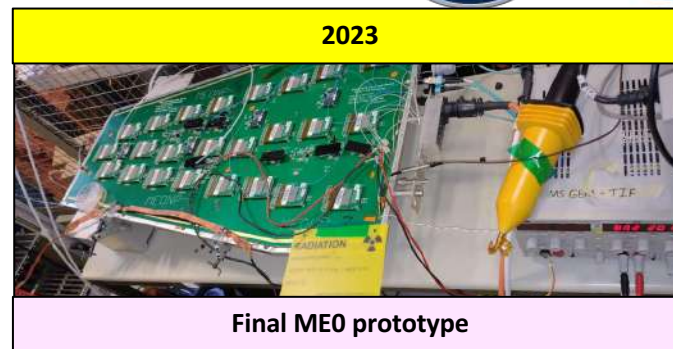
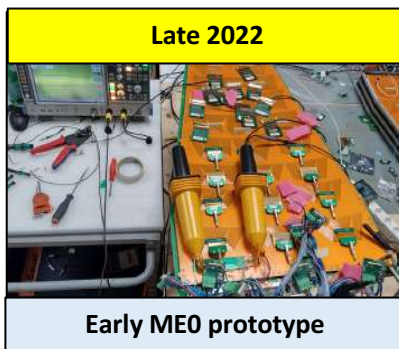
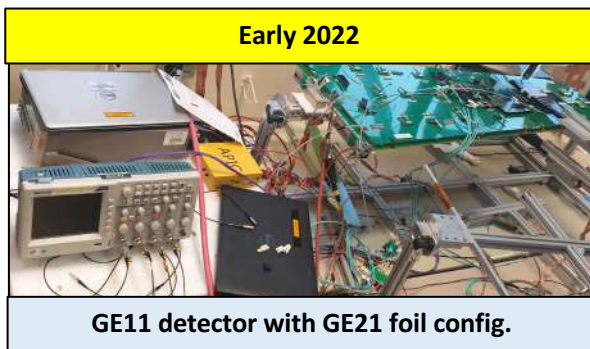
Large scale mitigation

- Need to implement an AC-coupling circuit with 1nF capacitor (and drain resistor) at the input of the electronics
- Parallel use of 1500-3000 input circuits significantly increase the capacitance of the induction gap
- Increased propagation probability
- Increase propagation energy



→ Rollback to previous GE1/1 protection





Discharge propagation probability:

In total:

- More than 5000 discharges provoked on GEM3 with HIP

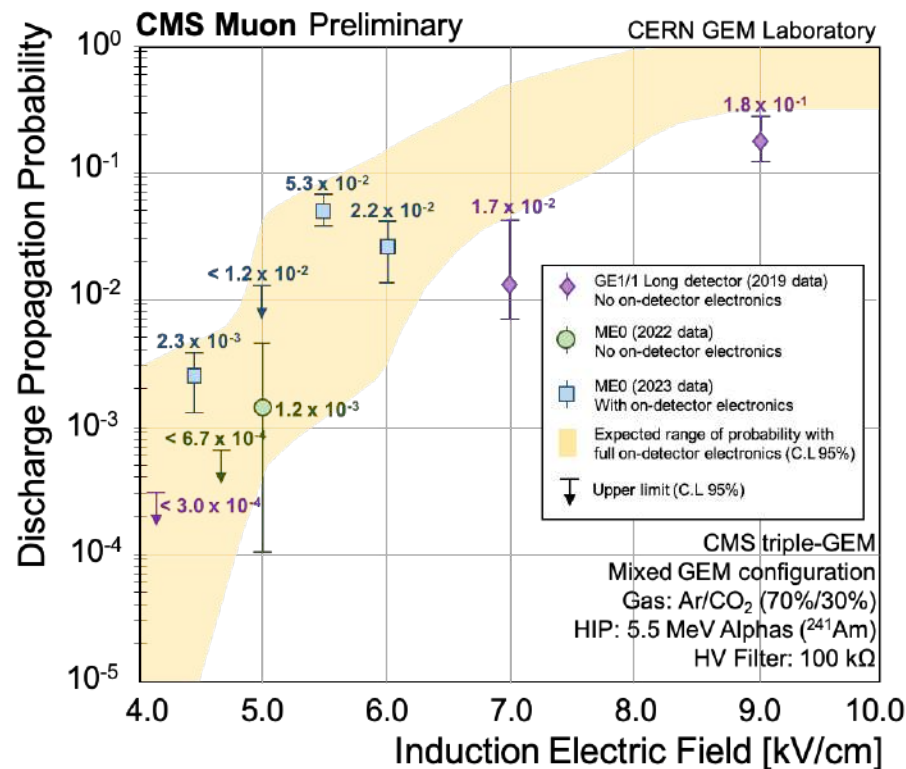
→ **Propagation probability : 2.28×10^{-3}** (at nominal gain 2×10^4 in Ar/CO₂)

VFAT Damage probability:

In total:

- > 120 confirmed propagations
- No channel damage observed

→ **Damage probability upper limit: 2.4×10^{-2}**
(expecting same or better than 3.0×10^{-2} from GE1/1)



Mitigations Overview

$P_d = 1.24 \times 10^{-9} \pm 1.16 \times 10^{-9}$
 (average of the two sets of tests we performed)
 Measured with $E_{\text{deposited}} \sim 350 \text{ keV}$

Factor based on
the RO coupling
circuit

Factor based on
the electronics
protection circuit

Factor based on the optimization of
the internal electric fields

Work in progress

HIP with
 $E_{\text{deposited}} > 30 \text{ keV}$

Assuming a HL-LHC
duty cycle = 0.33

Factor based on the
GEM foil design

System	HIP rate $R_{\text{HIP}}^{\text{max}}$	Disch. probability P_d	Discharge rate R_d^{max}	Number of disch. per year (per module)	Transfer propagation probability	Induction propagation probability	Damage probability	Improvement factor (E_{field} optimization)	Number of damaged RO channels per 10 year	Fraction of damaged RO channels per 10 year
(Unit)	Hz/sector	-	Hz/sector	y^{-1} /sector	-	-	-	-	$(10\text{y})^{-1}$	$(10\text{y})^{-1}$ (%)
Slice test*	3.15×10^3	1.24×10^{-9}	3.90×10^{-6}	39	0.5	1	0.95	1	185 per VFAT(128 ch)	100 %
GE11	3.15×10^3	1.24×10^{-9}	3.90×10^{-6}	987	0.5	1	0.03	1	148 per module	4.82 %
GE21	1.92×10^3	1.24×10^{-9}	2.38×10^{-6}	405	2.3×10^{-3}	1	2.4×10^{-2}	1	0.2 per module	~ 0.01 %
MEO	2.36×10^5	1.24×10^{-9}	2.93×10^{-4}	25080	2.3×10^{-3}	1	2.4×10^{-2}	1	13 per module	~ 0.45 %

* Obsolete design – for comparison purpose

Improved by the double-segmentation
on GEM1 and GEM2

De-coupling capacitor +
drain resistor is not
optimal

Improved by VFAT
protection resistor and
optimized HV filter

Studies are on-going:
the improvement is
not yet quantified

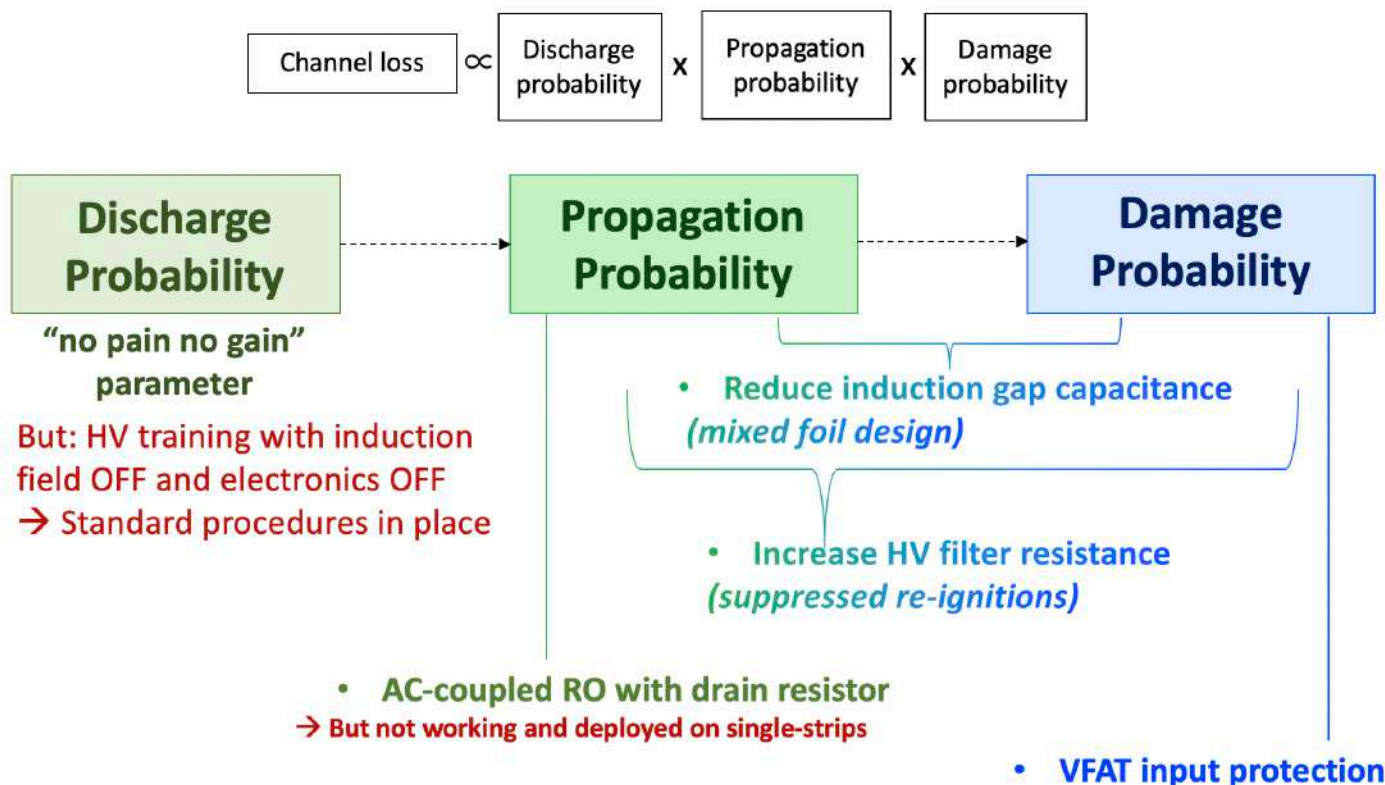
Note on the discharge rate:

- the table only takes into account discharges caused by incoming BKG particles
- Spontaneous discharges may occur at the beginning of the detector life due to the presence of dust and contaminants after the chamber movement/installation
 - A "training procedure" is in place to eliminate the dust and clean the foils in safe conditions

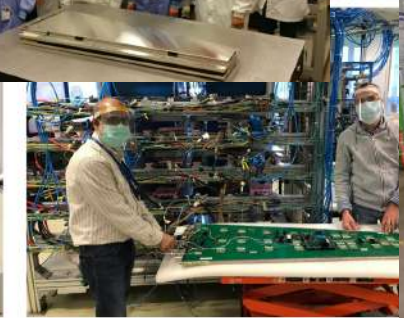
→ Discharges studies in the CMS GEM group

- Long experience → almost continuous studies in place since 2015-2016
- Developed/improved/standardized setups for discharge investigations (with the help of CERN GDD and other RD51 groups)

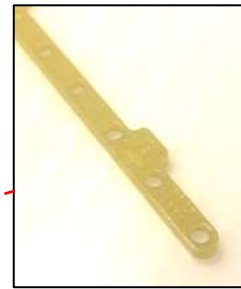
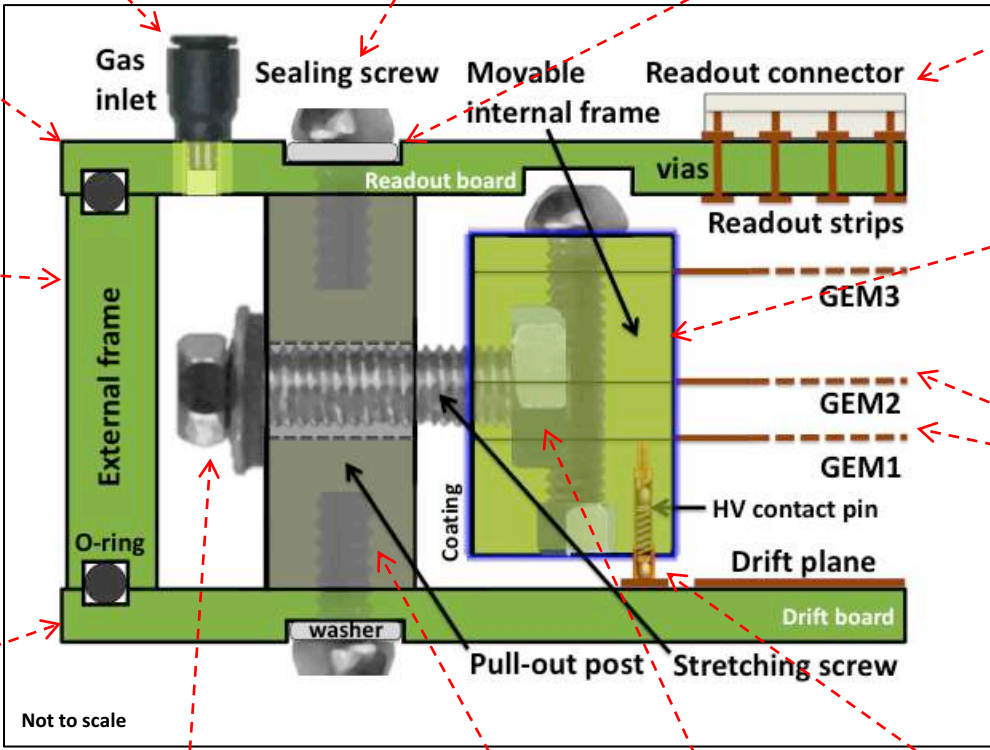
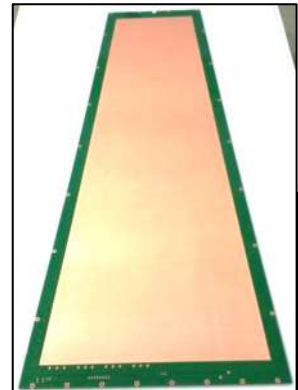
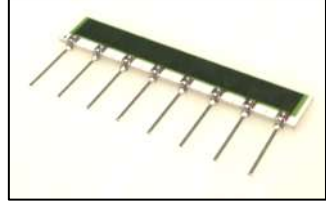
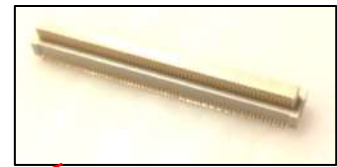
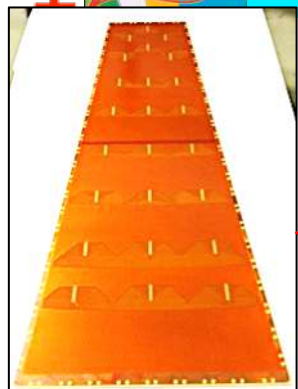
→ Mitigation Strategy



Thank you

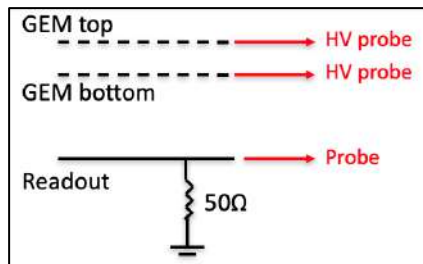
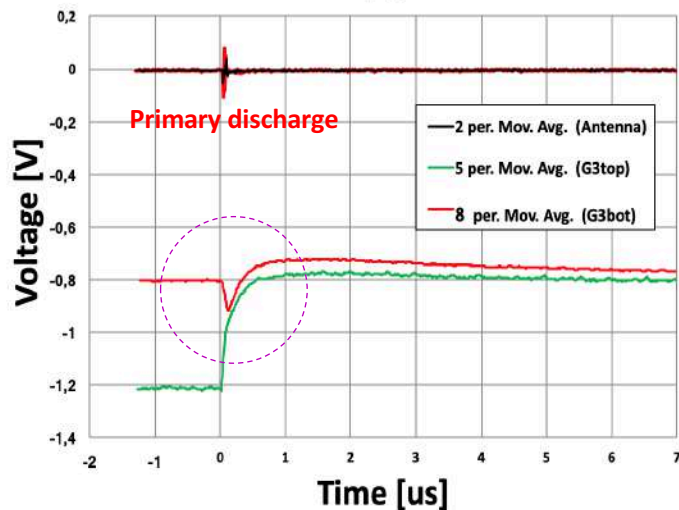


Detector Components

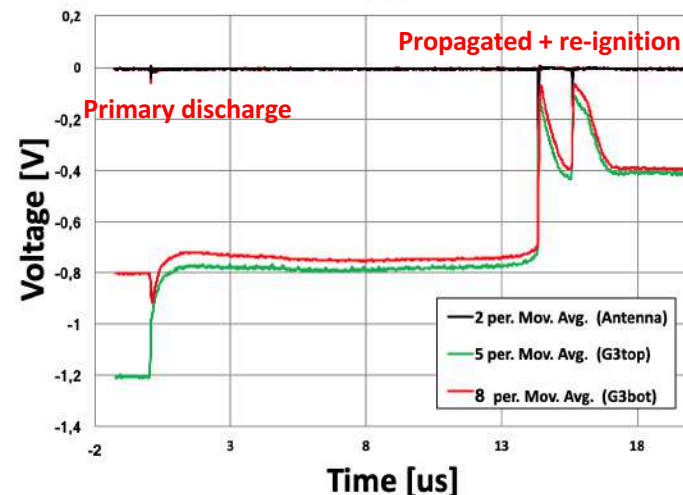


Discharge Propagation

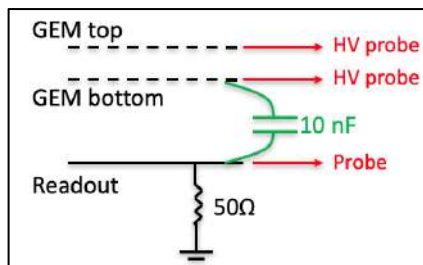
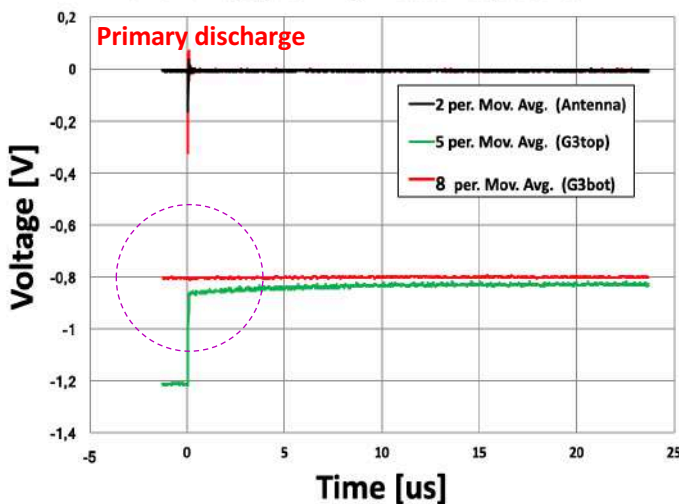
10x10 No Propagation



10x10 Propagation

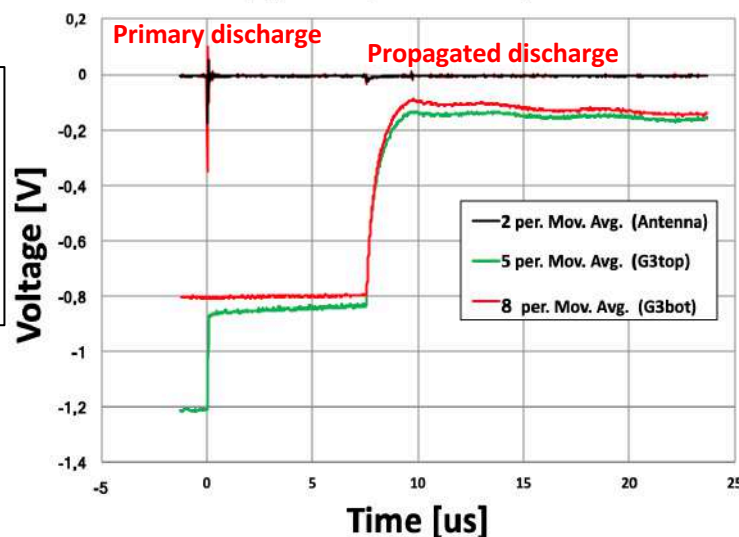


10x10 No Propagation - High Induction Capacitance



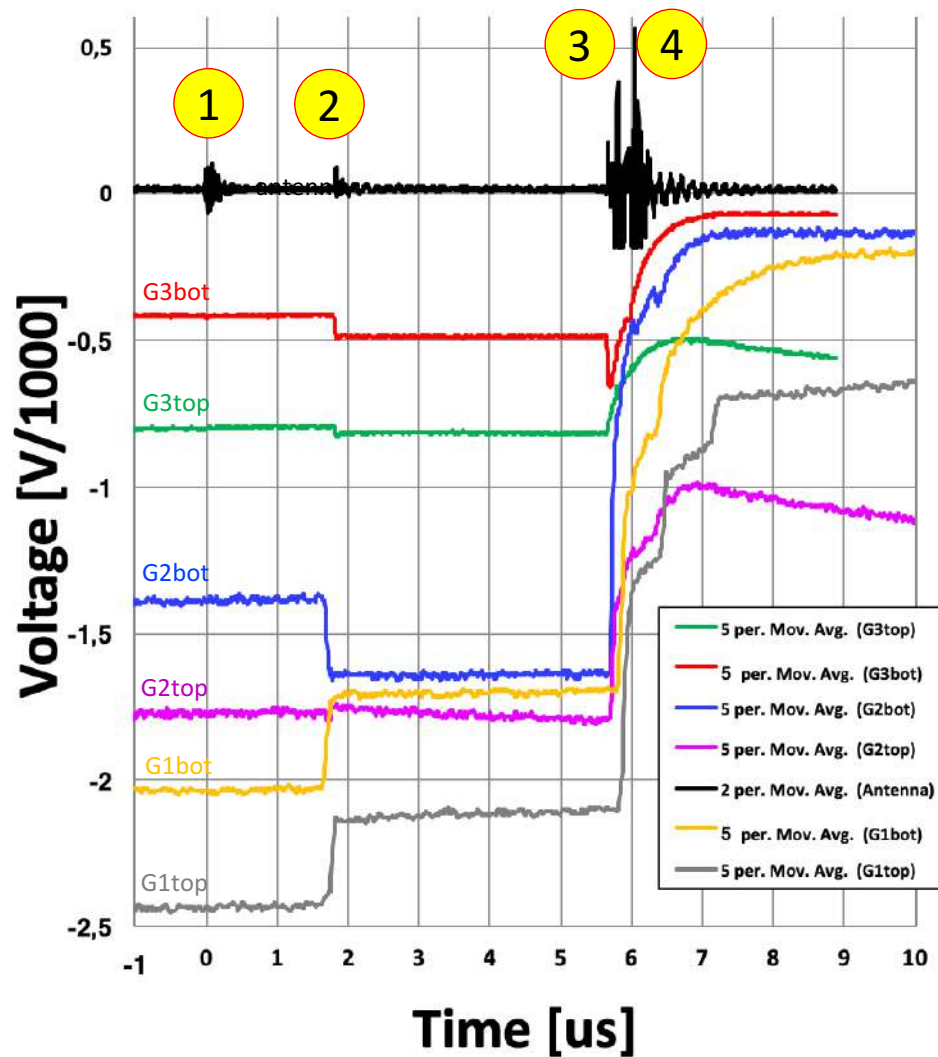
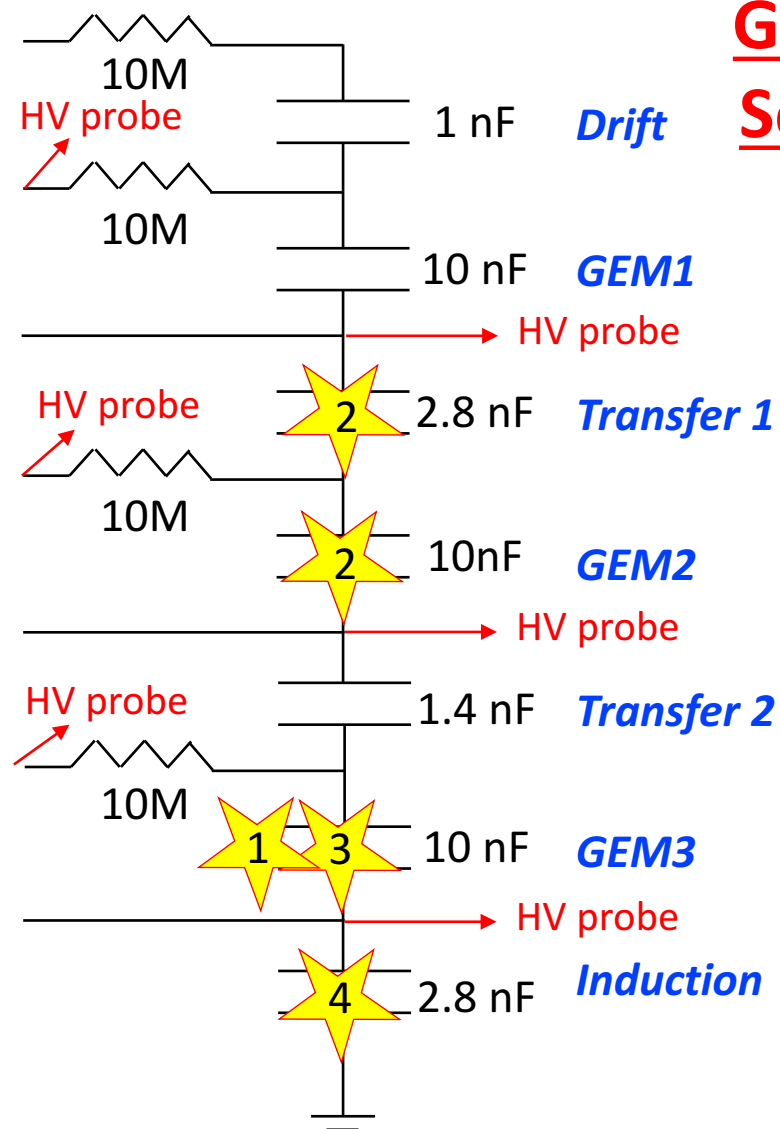
No voltage jump on G3bottom during the discharge

10x10 Propagation - High Induction Capacitance



Discharge Propagation

GE1/1 Setup

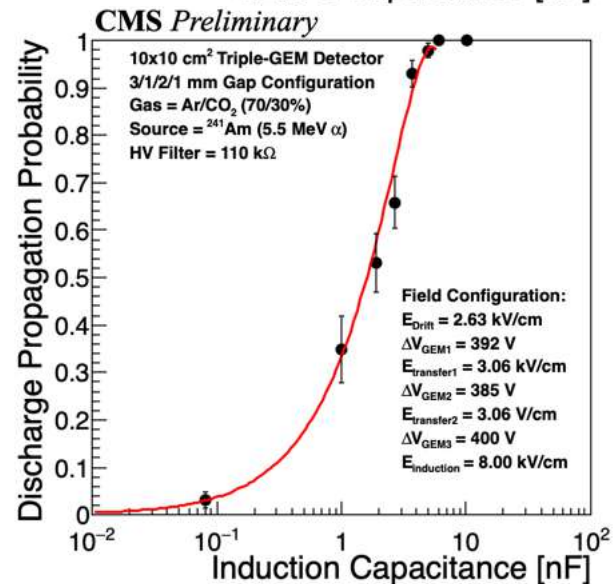
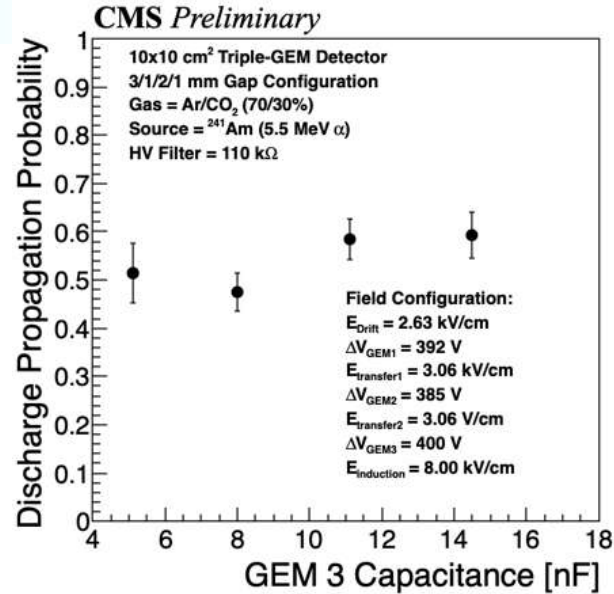


Propagation studies (2019-2021)

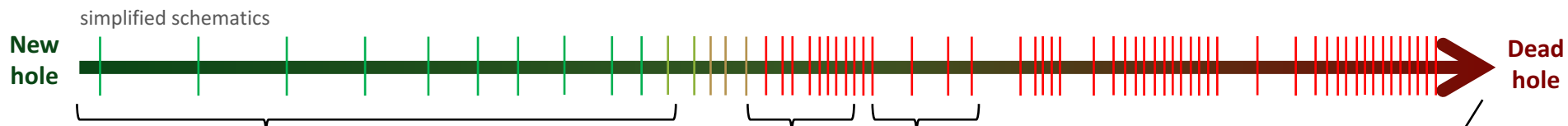


Further studies to understand differences between small and large chambers:

- No dependency with the GEM foil capacitance → no influence of the primary discharge energy
- Clear increase of the propagation probability with the induction capacitance → i.e. sufficient amount of energy on the foil to feed the precursor current and trigger discharge propagation
- All measurements indicate that the discharge propagation is more likely to happen in large foils due to the availability of energy directly stored in the foil



Discharge Effects

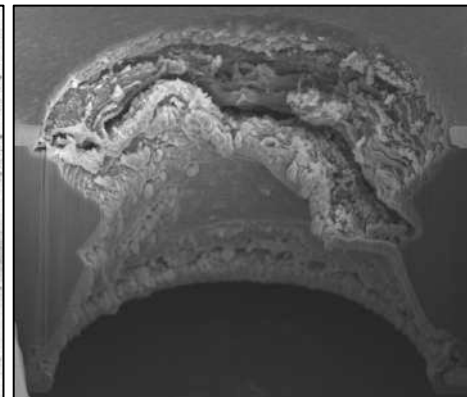
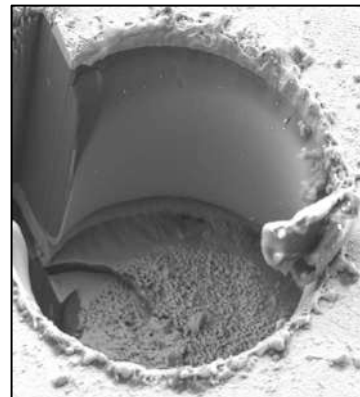
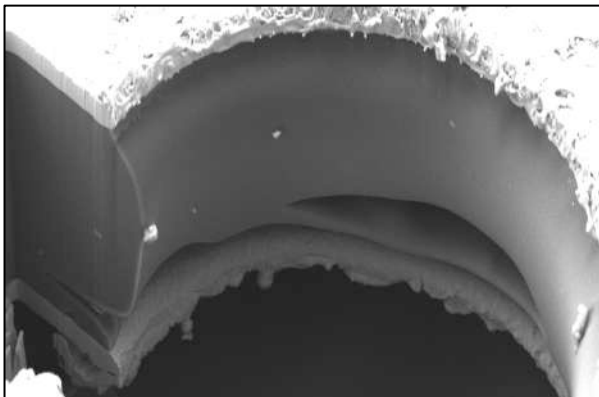
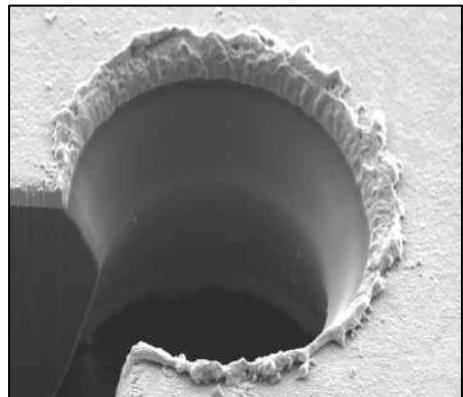
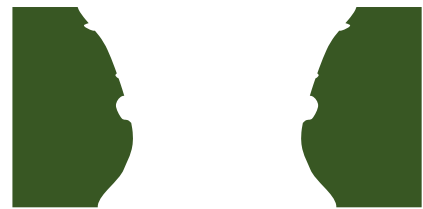
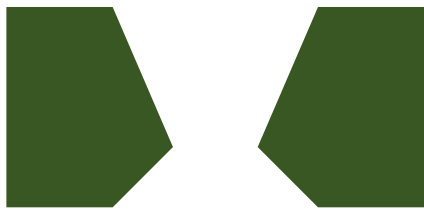


“Stable” Phase:
 - Progressive and uniform surface etching
 - Clean internal surface

“Weak State” :
 - Presence of cavities and defects on the internal surface of the PI
 → Self-discharging

“Strong State:
 - Attenuation of cavities and defect due to uniform surface etching
 → Curing effect

“Shorted”:
 - Strong irregularities and defects

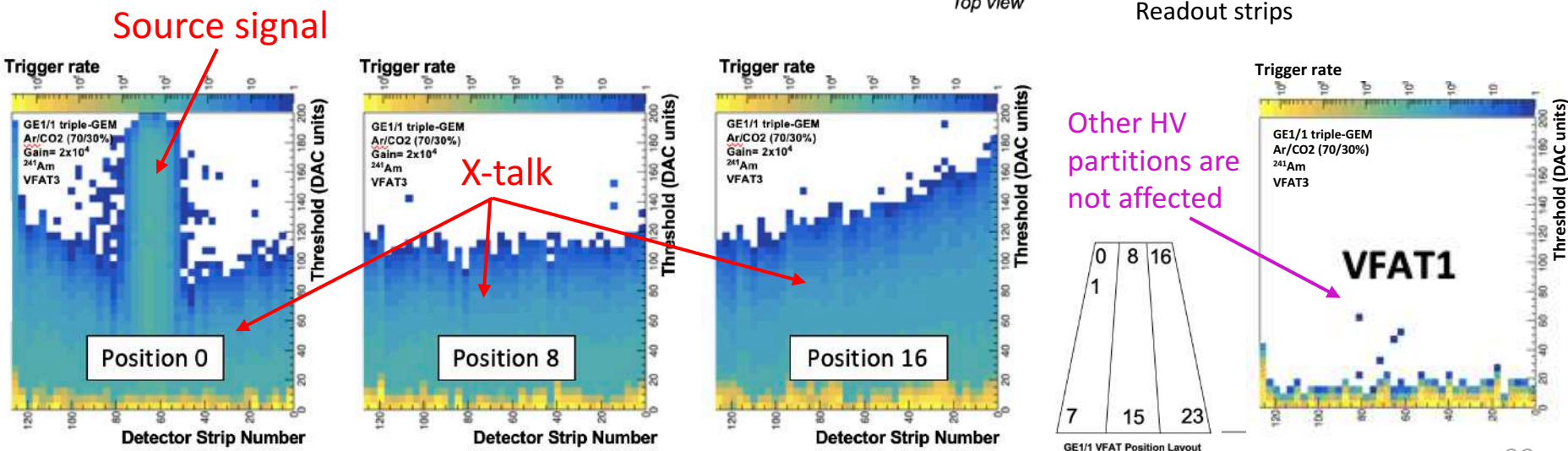
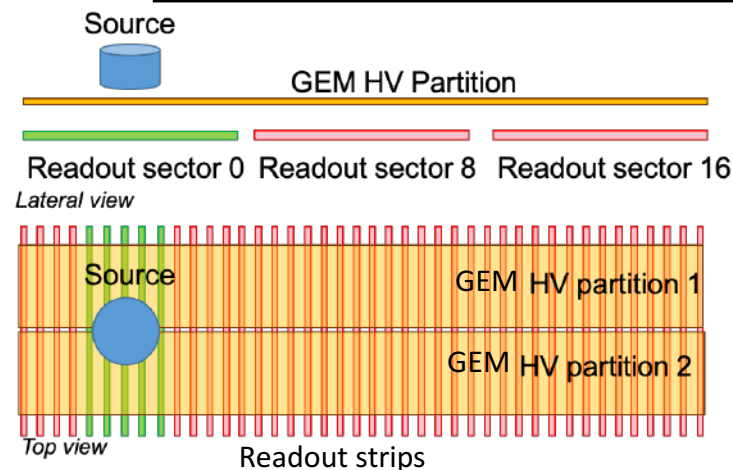


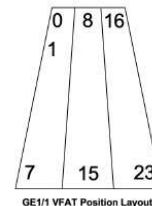
Crosstalk – General Description

Side effect of using double-segmented design on GEM3:

- Reducing the size of the HV segments on the last GEM increases the HF impedance to ground:
 - Induces **cross-talk**
 - All strips facing the **same HV partition** can suffer crosstalk
 - In case of **large signals (HIP)**, the corresponding crosstalk signals can trigger the electronics and make the channels unusable for several BX

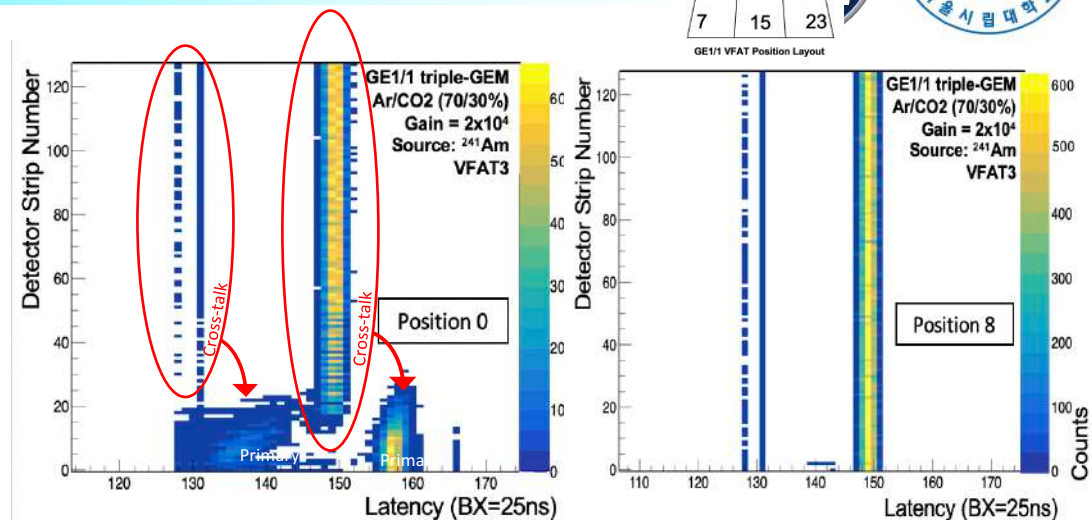
Start of a R&D campaign to cope with the crosstalk issue





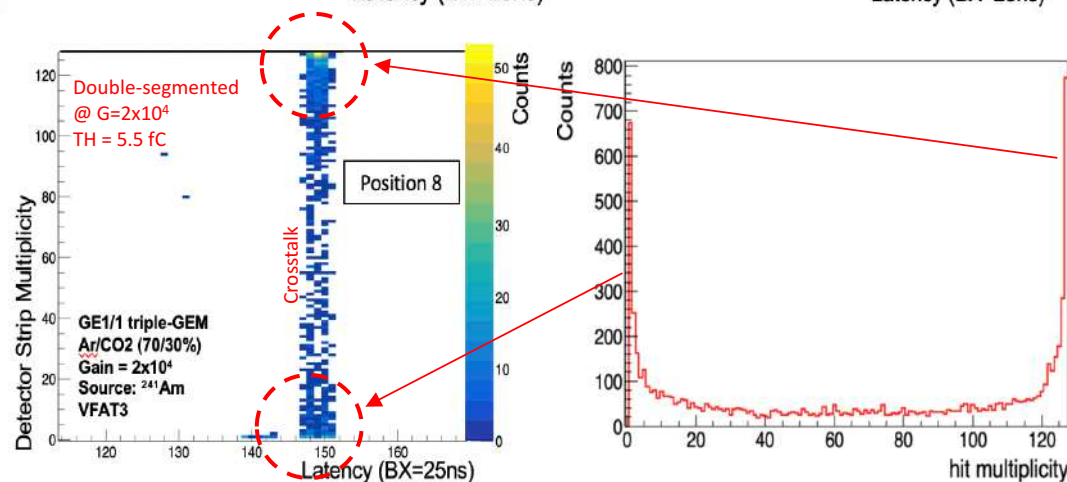
Timing characteristics:

- Each primary signal structure has its own cross-talk structure coming after **10 BX** (250 ns)
- Probability of cross-talk depends on the amplitude of the primary signal (expected)



Range and probability:

- Eventually, all channels sharing the same HV partition are affected by the cross-talk
- On average, **61%** of the channels are seeing the same crosstalk signal for a given event



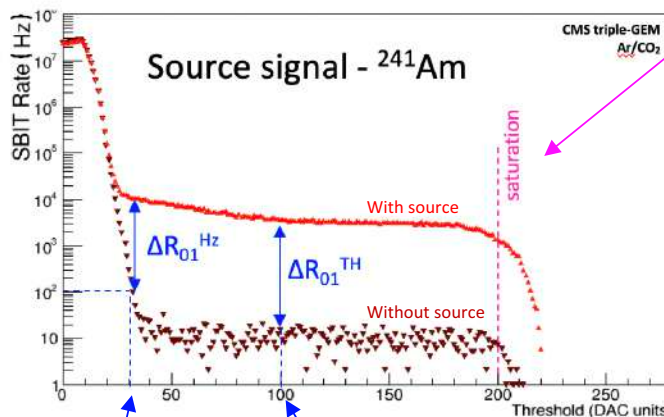
Crosstalk signals are typically affecting **61% of the channels** sharing the **same HV segment**, with a **delay of 250 ns** with respect to the original signal

Crosstalk - Probability



Probability measurement:

- At fixed threshold to estimate the rate for the highest amplitude signals
- At nominal threshold (= 100Hz of noise)



ARMDAC 100 = 14.1 ± 2.1 fC
(may vary a bit from one VFAT to another)

ARMDAC 30 = 4.4 ± 0.6 fC
(may vary a bit from one VFAT to another)

Saturation:

→ Not possible to **quantify the max amplitude** of a signal if the SBIT rate drops around 200 DAC units

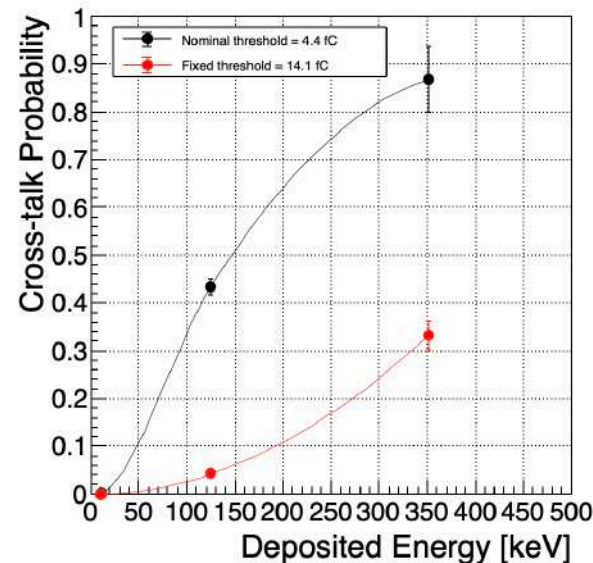
→ A “plateau like” rate profile indicates that the signal is above the VFAT range

Crosstalk probability:

$$P_{XT}^{TH} = \frac{\Delta R_{neighbour}^{TH}}{\Delta R_{source}^{TH}} \rightarrow \text{at fixed threshold 100 DAC units}$$

$$P_{XT}^{Hz} = \frac{\Delta R_{neighbour}^{Hz}}{\Delta R_{source}^{Hz}} \rightarrow \text{at nominal threshold 100 Hz noise}$$

Crosstalk probability in double-segmented foils becomes problematic for energy deposits above **30 keV**. X-rays and lower ionization particles **do not trigger** crosstalk



LHCb Experience:

- Triple-GEM $\sim 480 \text{ cm}^2$
- 3/1/2/1 configuration
- HV segments top $\sim 80 \text{ cm}^2$
- HV segments bottom \sim none
- Induction Capa $\sim 0.2 \text{ nF}$

KLOE-2 Experience:

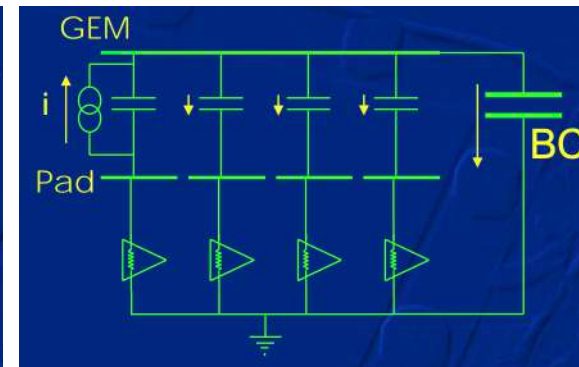
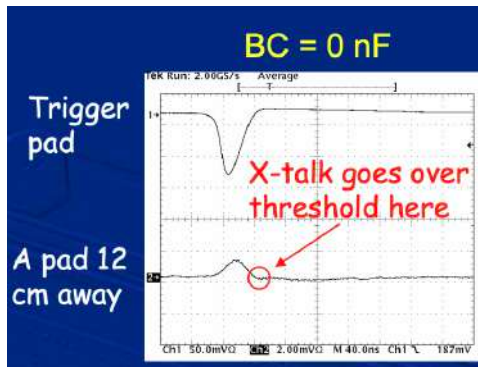
- Triple-GEM $\sim 2450 \text{ cm}^2$ (cylindrical)
- 3/2/2/2 configuration
- HV segments top $\sim 105 \text{ cm}^2$
- HV segments bottom $\sim 615 \text{ cm}^2$
- Induction Capa $\sim 0.8 \text{ nF}$

Crosstalk mitigation:

- Use of a **blocking capacitor** between G3 bottom and GND to bypass the induction gap:
 LHCb: $C_b = 0.7 \text{ nF}$
 KLOE-2: $C_b = 2.2 \text{ nF}$

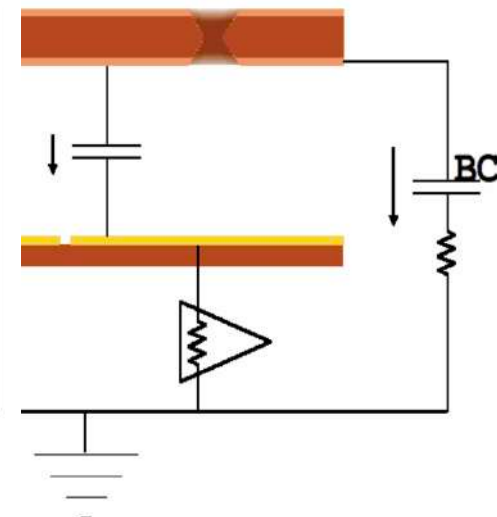
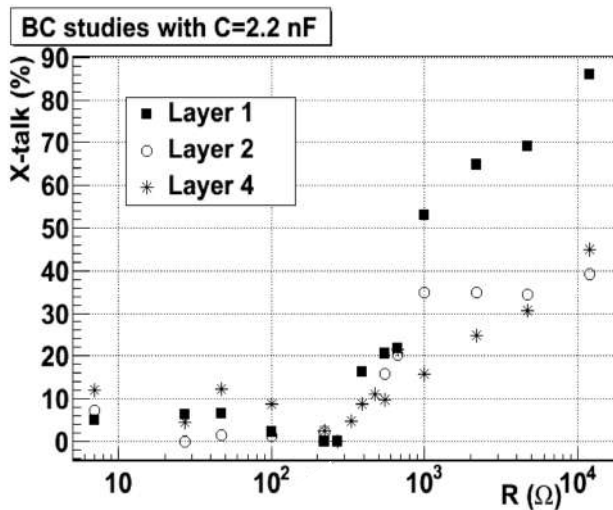
A. Cardini for the LHCb Collaboration (2006)

<https://indico.cern.ch/event/473/contributions/1983755/attachments/954021/1353774/Cardini.pdf>



G. Morello for the KLOE-2 IT group(2013)

[https://indico.cern.ch/event/258852/contributions/1589820/attachments/456014/632021/MPGD20213_morello.pdf](https://indico.cern.ch/event/258852/contributions/1589820/attachments/456014/632021/MPGD2013_morello.pdf)



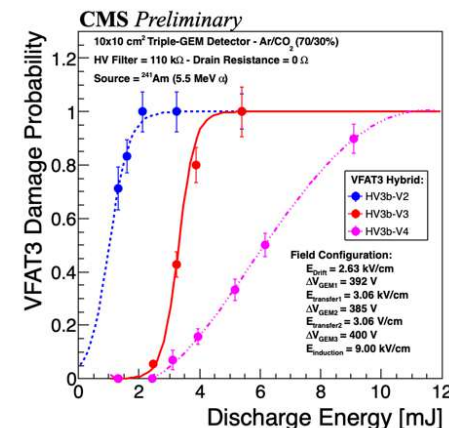
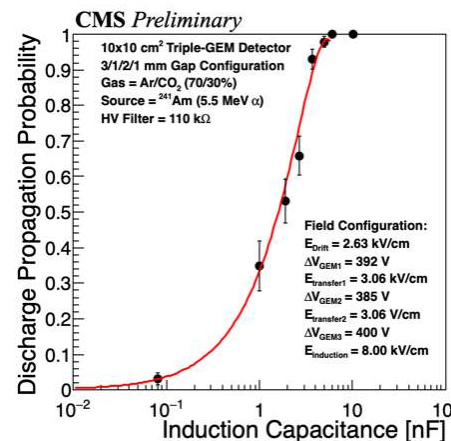
Technical limitations:

- GE2/1: 40 to 80 HV segments per foil → the blocking circuit must be inside the gas volume
- Significant re-design of the foils (add space for the RC components, bring GND line on the foil)
- Significant re-design of other detector components (DRIFT board, Mechanics etc ...), possible reduction of the active area
- Introduce new weaknesses (e.g. long term failure of the capacitor)
- **Hard to find nF capacitors which can fit in a 1mm gap (including safe distance with other electrodes)**

Conceptual limitations:

- Adding the blocking capacitor means increasing the gap capacitance by a factor 3:
 - Increase of the **discharge propagation probability** (defeats the primary purpose of the double-segmented design)
 - Increase of the **discharge energy**, i.e. the probability to damage the electronics in case of propagation

	Induction C_i (nF)	Blocking C_b (nF)
LHCb	~ 0.2 nF	0.7
KLOE-2	~ 0.8 nF	2.2
GE2/1	~ 2 - 3 nF	> 6 - 9 nF



3 configurations are compared:

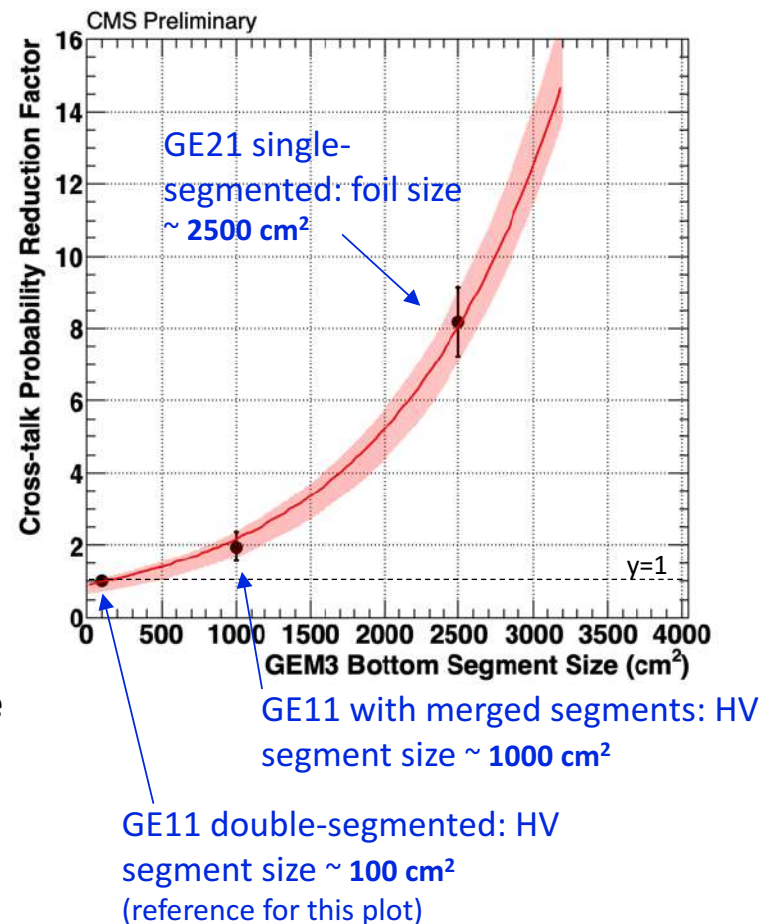
- GE11 double segmented; segment size $\sim 100 \text{ cm}^2$
- GE11 with merged segments; segment size $\sim 1000 \text{ cm}^2$
- GE21 single segmented; “segment” size $\sim 2500 \text{ cm}^2$

Improvements:

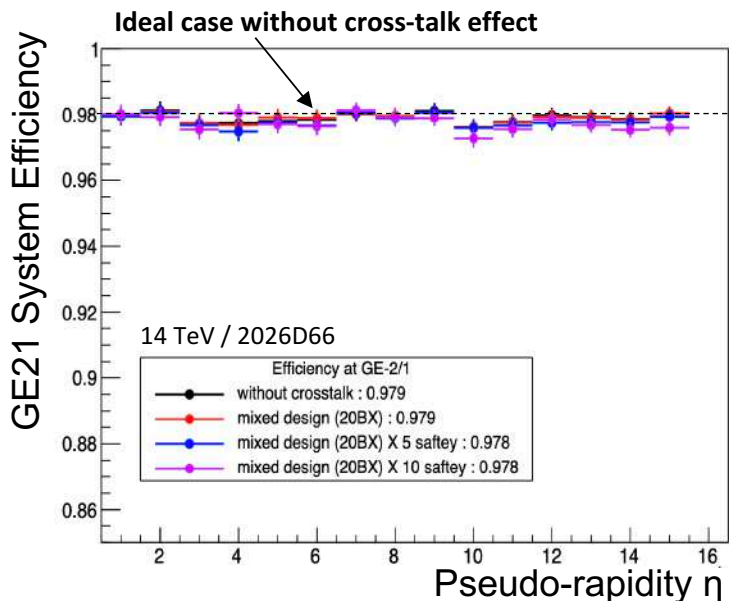
- Increasing the HV segments size helps to evacuate the crosstalk current and “dilute” the crosstalk effect over a larger surface
- Maximum segment size: $\sim 1200 \text{ cm}^2$ (i.e. 2 segments per foil)
 - Crosstalk probability reduced by a factor ~ 2.5
 - Crosstalk amplitude reduced to less than $\sim 20\text{-}25 \text{ fC}$

But the improvement is much less compared to a regular single segmented foil:

- Unnecessary **complication** of the design
- Both options would give **poor discharge mitigation**



The improvement of the crosstalk is **not sufficient** to justify the increasing of the HV segment size
 → better results are obtained by completely removing the bottom segmentation
 → **The real choice is between single-segmented or double-segmented with fine segments**



Simulation parameters:

- Event samples for $Z \rightarrow \text{Mumu}$ @ 14 TeV
- The **HIP rate** is estimated from the BKG simulation, convoluted with the crosstalk probability vs. **deposited energy** (> 83 keV).
- Each strip can possibly see the crosstalk from **the entire module**
- **Inoperative time** of **20 BX** based on the electronics simulation

First order approximation given by:

$$\text{Probability of inactive RO per event} : P_{DT} = \frac{HIP_{rate}}{BX} \times Prob_{XT} \times InoperativeTime$$

← Rate Normalized to 1 BX

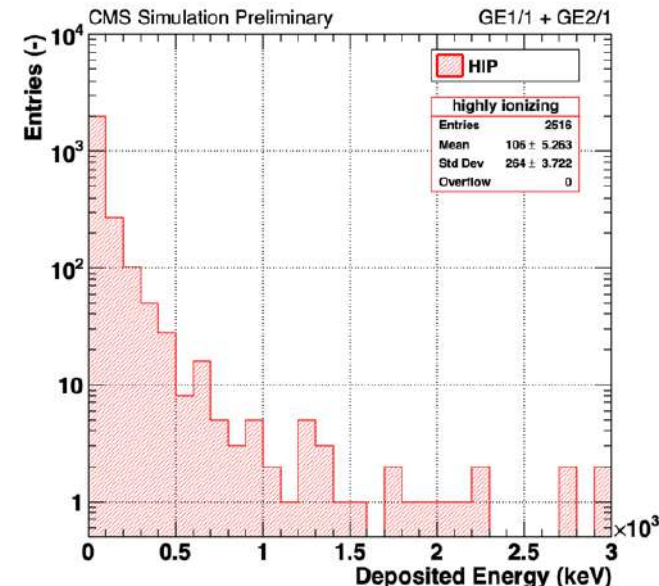
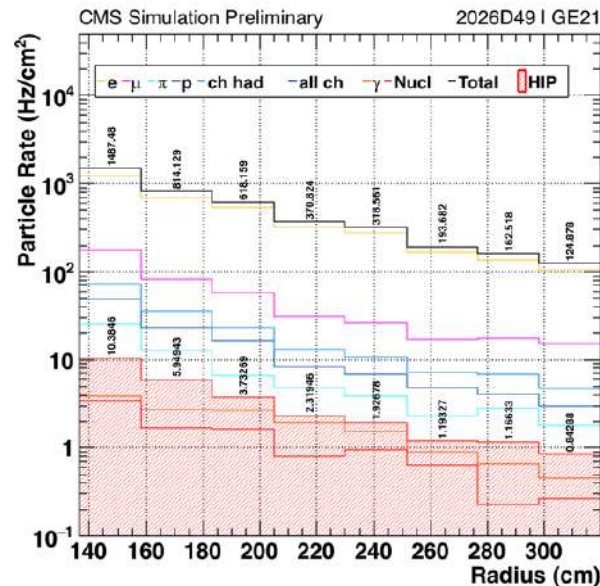
$$\text{Then the real chamber efficiency is} : Eff_{real} = Eff_{ideal} \times (1 - P_{DT})$$

The maximum **efficiency drop** due to the crosstalk effect is of the order of **0.04 %** at the highest eta (without safety factor)
 → **Successful mitigation**

Evaluation of the Crosstalk rate in CMS:

- Prediction of the total particle rate per eta partition of a single GE2/1 chamber
- Simulation including neutron background hits has been performed with GEANT
 - Total hit rate of Highly Ionizing Particles (HIPs) (mostly protons and nuclei) depositing 30 keV or more
- The HIP rate can be convoluted with the energy-deposit dependent probability to create a cross talk signal to obtain the prediction of the cross talk signal rate

BKG population susceptible to **trigger crosstalk** is derived from the 30 keV energy cut: up to **10.4 Hz/cm²** in the hottest GE21 region. The average energy deposit for this population is **107 keV**



GEANT4 based simulation model including the latest CMS configuration (with all subdetectors upgrades)
 CMSSW 11_0_0_pre13 Min Bias collisions with hit time 100ms